

# Comparison of Three Types of Startup Circuits for Self-biasing MOS Reference Current Sources

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Gunma University

Jedat Inc.



# OUTLINE

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- **Research Background**
- **MOS Drain Current Temperature Characteristics**
- **Gunma University (GU) Reference Current Source**
- **Three Types of Startup Circuits**
  - **Startup Circuit 1**
  - **Startup Circuit 2 (CMOS inverter usage)**
  - **Startup Circuit 3 (Capacitor usage)**
- **Conclusion**

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# Research Background

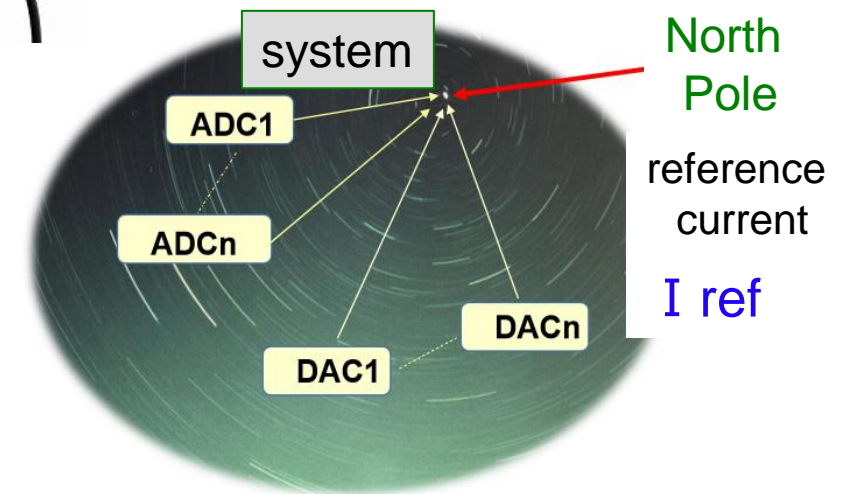
Reliability issues in electronic circuits

- Process
- Voltage
- Temperature



First, we present

**MOS Reference Current Sources  
Insensitive to Supply Voltage and Temperature**



Next,

**Consider and Compare the Three Types of Startup Circuits  
in terms of **Chip area**, **Power consumption**, and **Startup operation certainty**.**

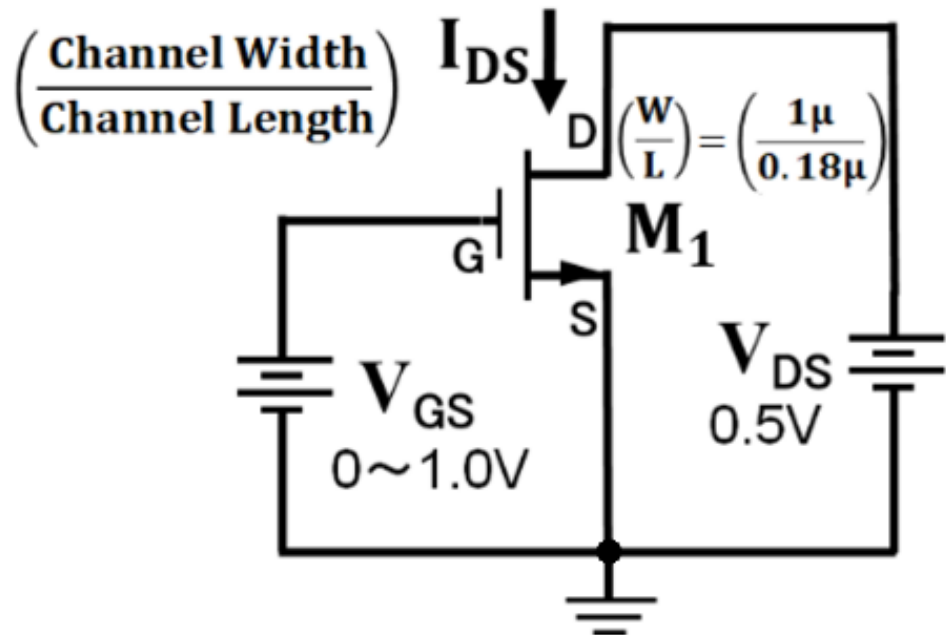
# OUTLINE

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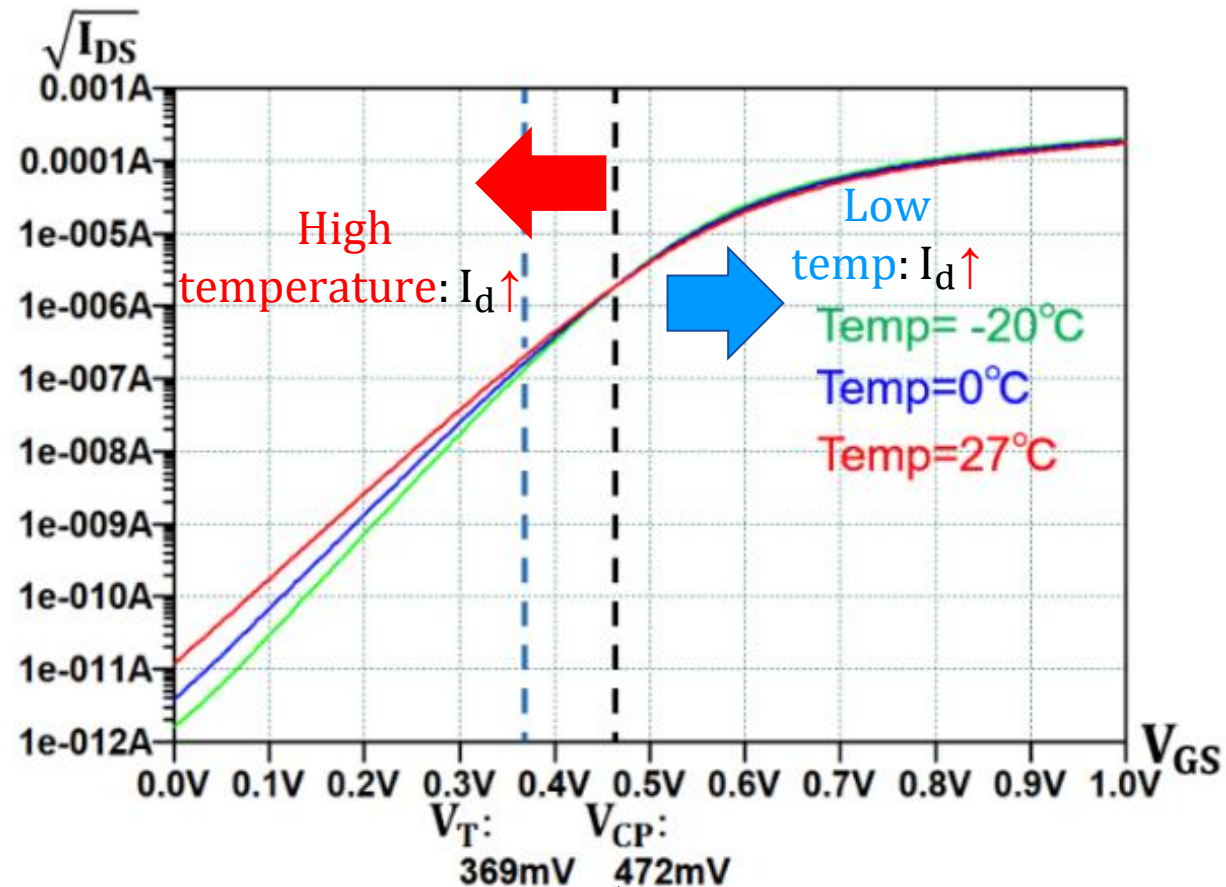
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# MOS Drain Current and Gate Voltage

Simulated drain current  
temperature characteristics



TSMC 0.18 $\mu$ m BSIM3v3 CMOS SPICE parameters



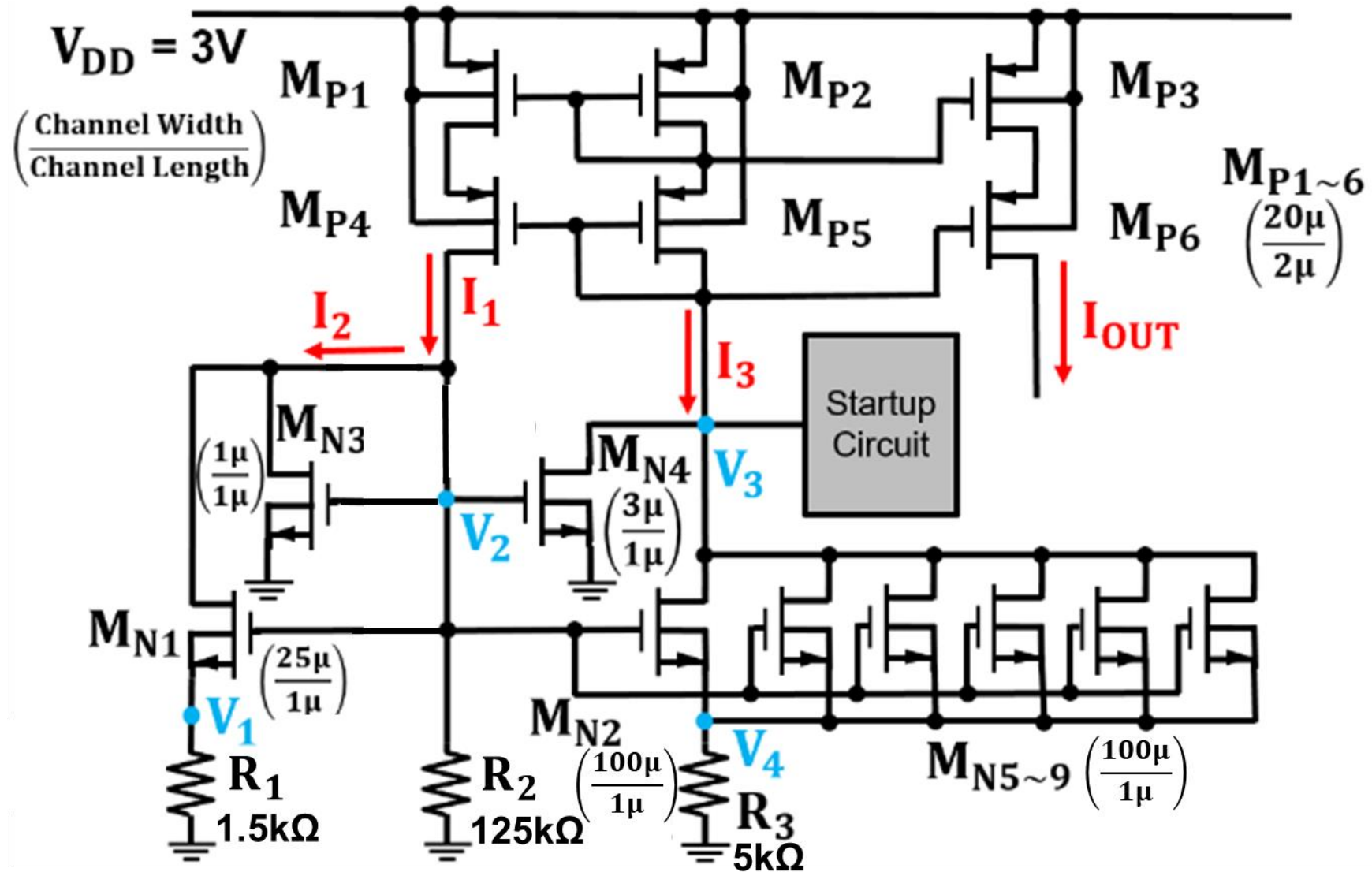
At  $V_{CP}$  (472mV): Drain current is fixed  
against temperature change

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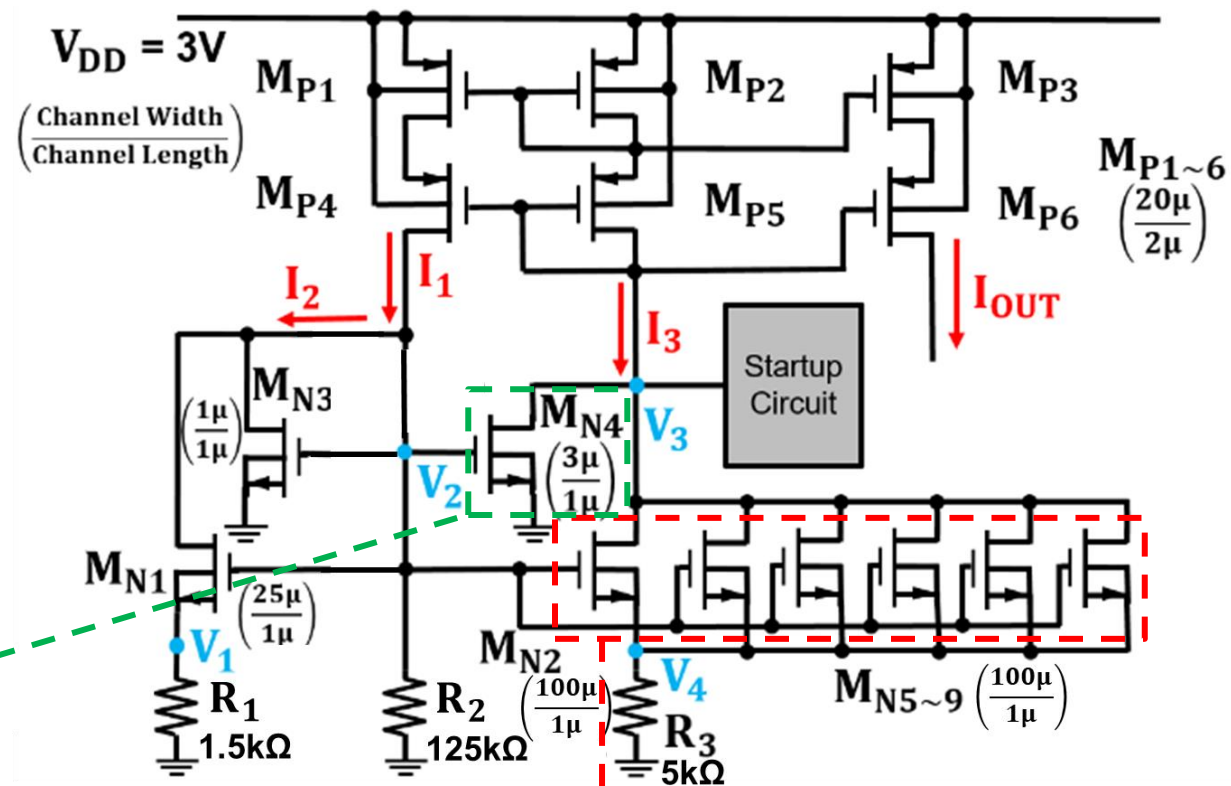
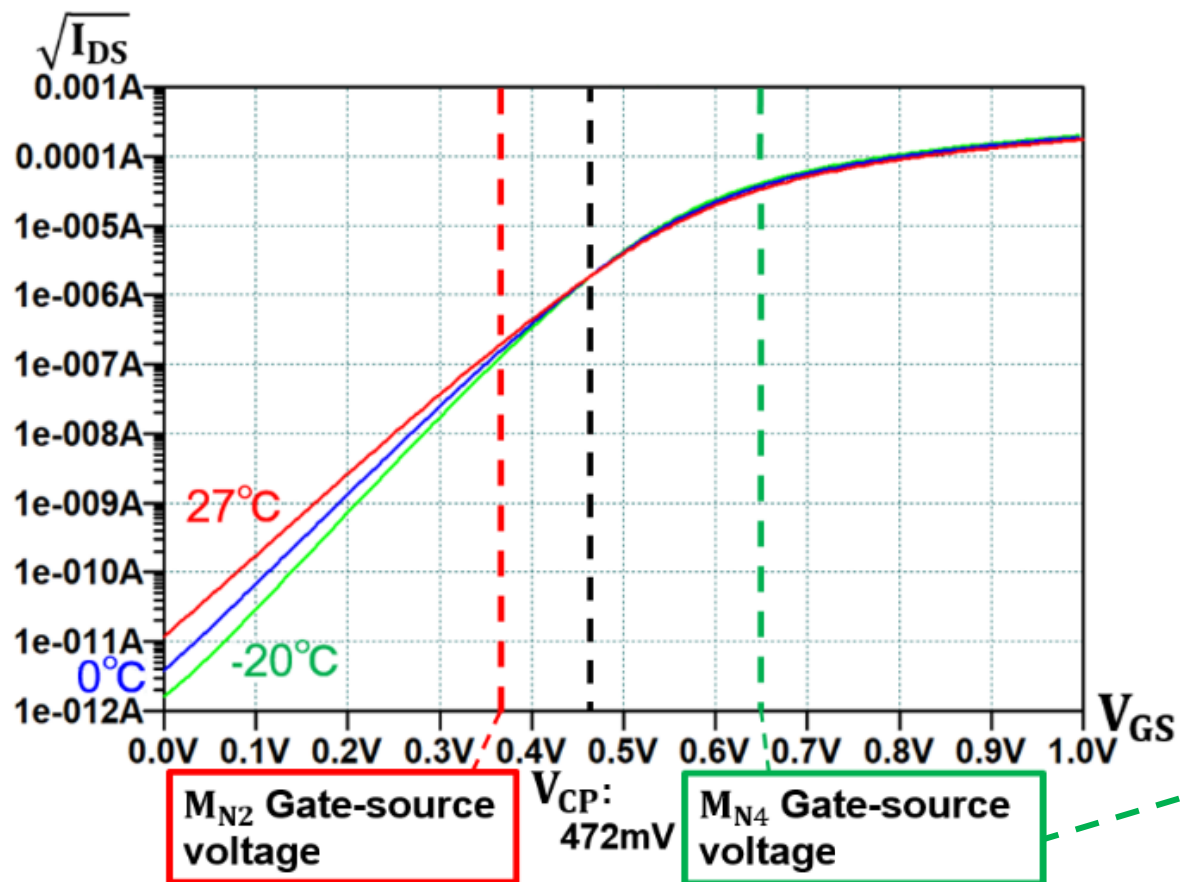
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# Gunma University (GU) Reference Current Source 8/44

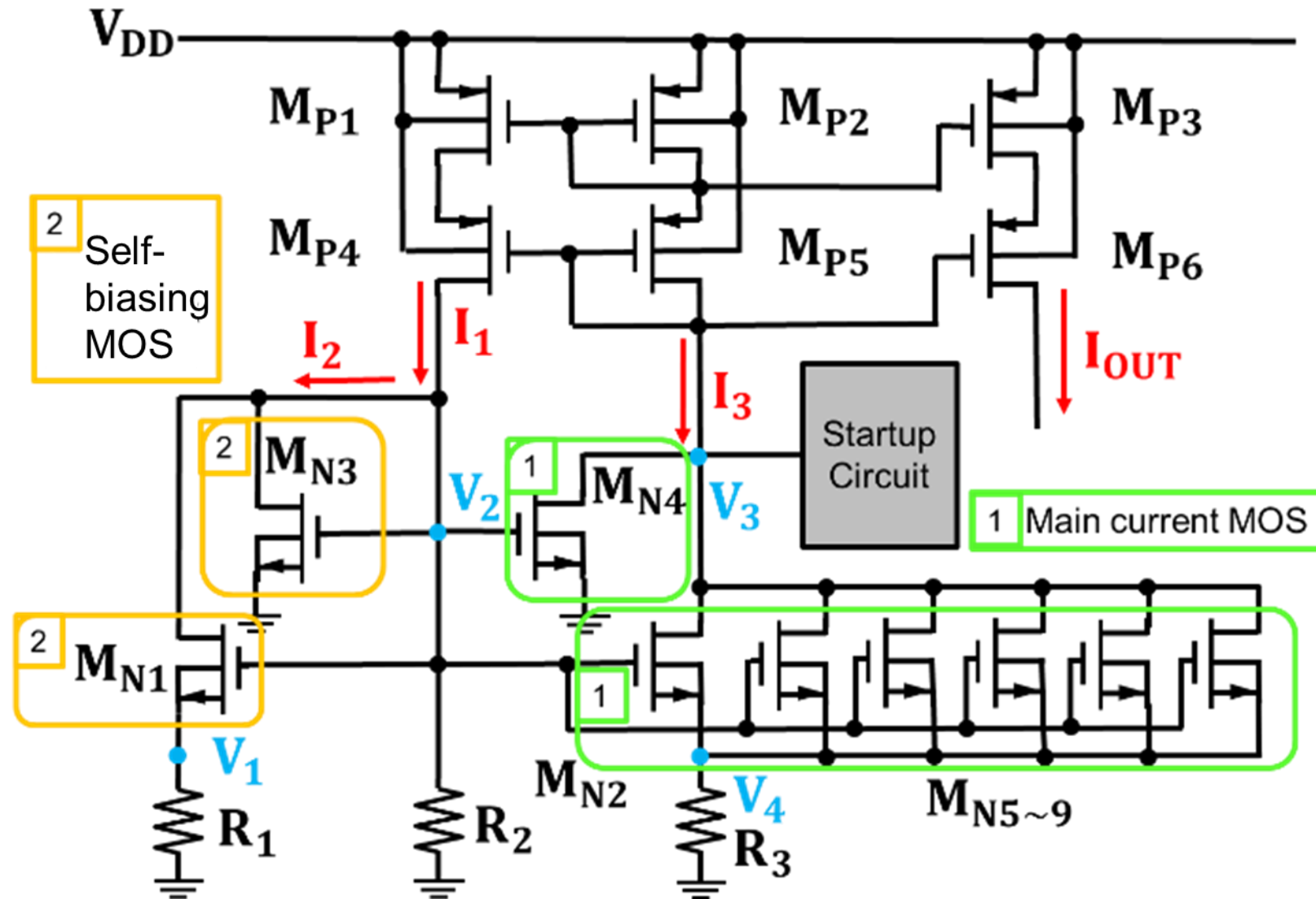




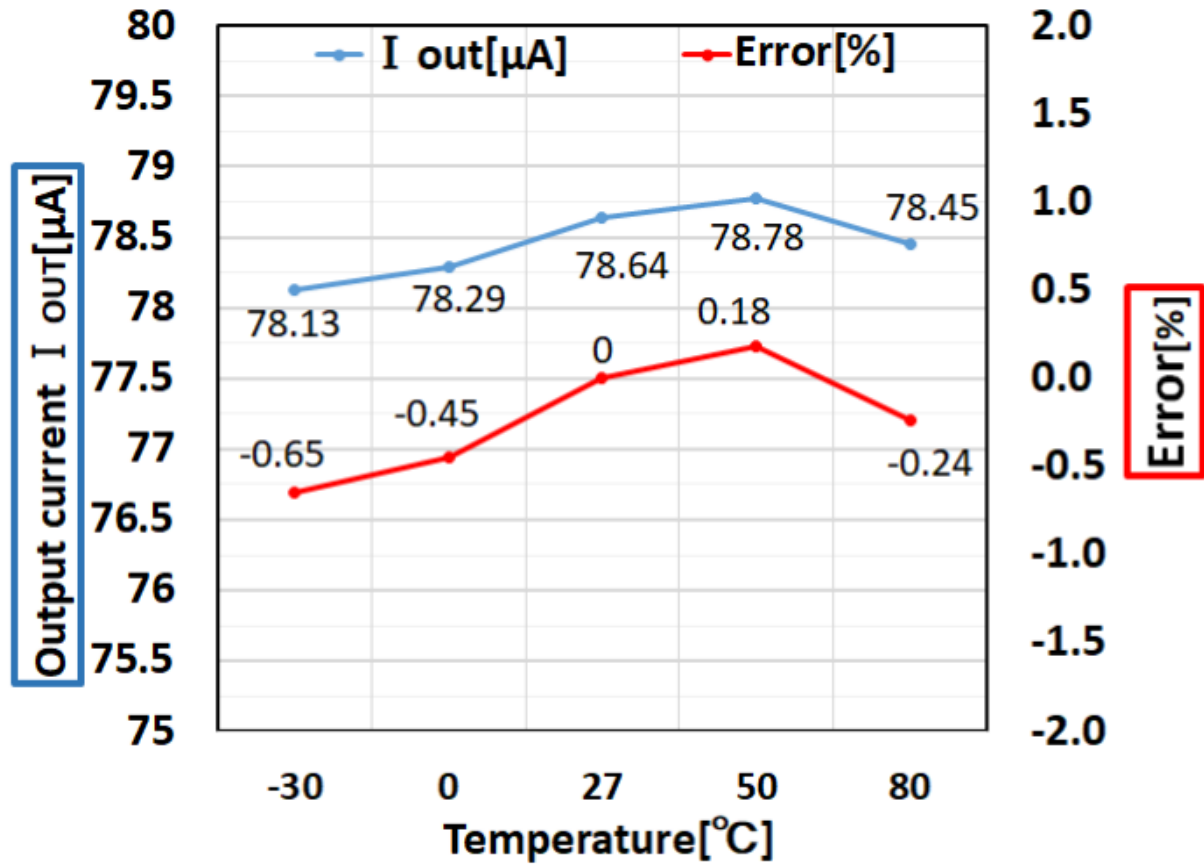
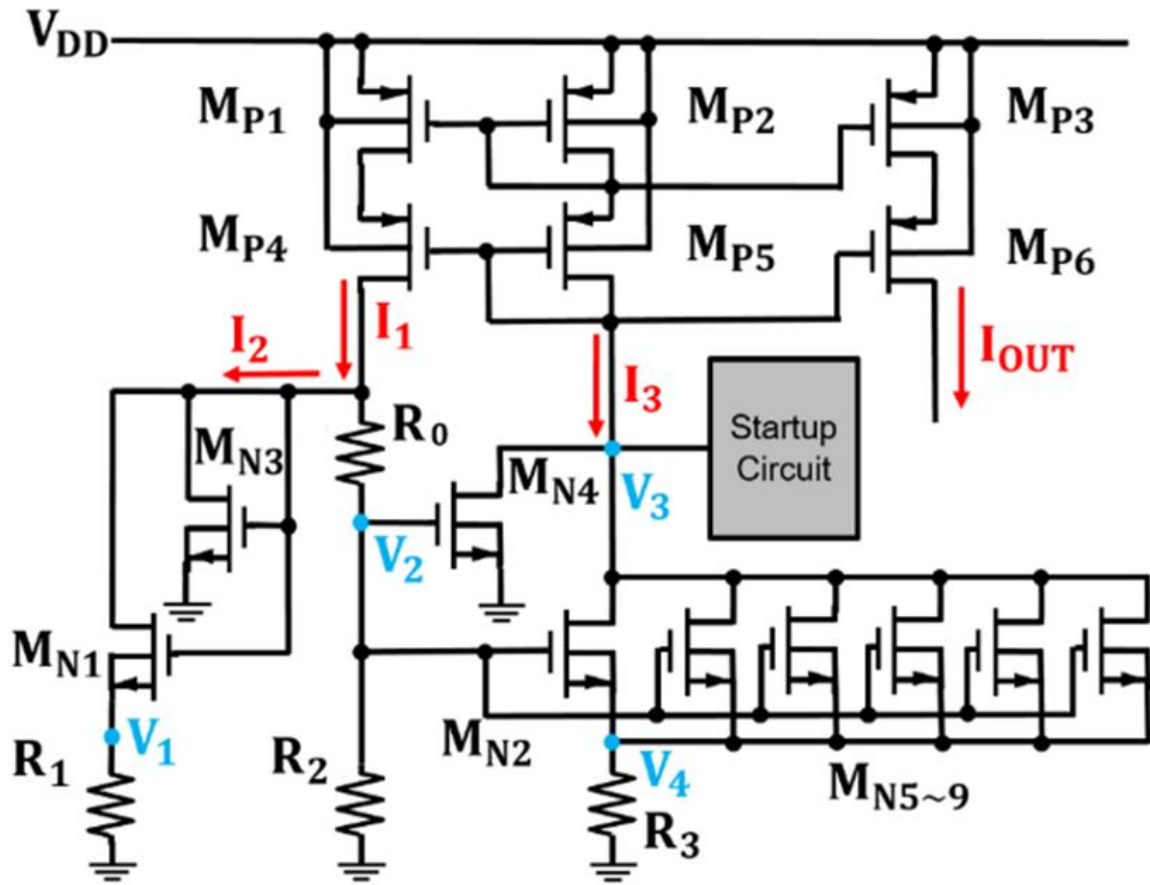
# Temperature characteristic cancellation



# $V_2$ Suppression by Self-biasing MOS



# Output Current $I_{OUT}$

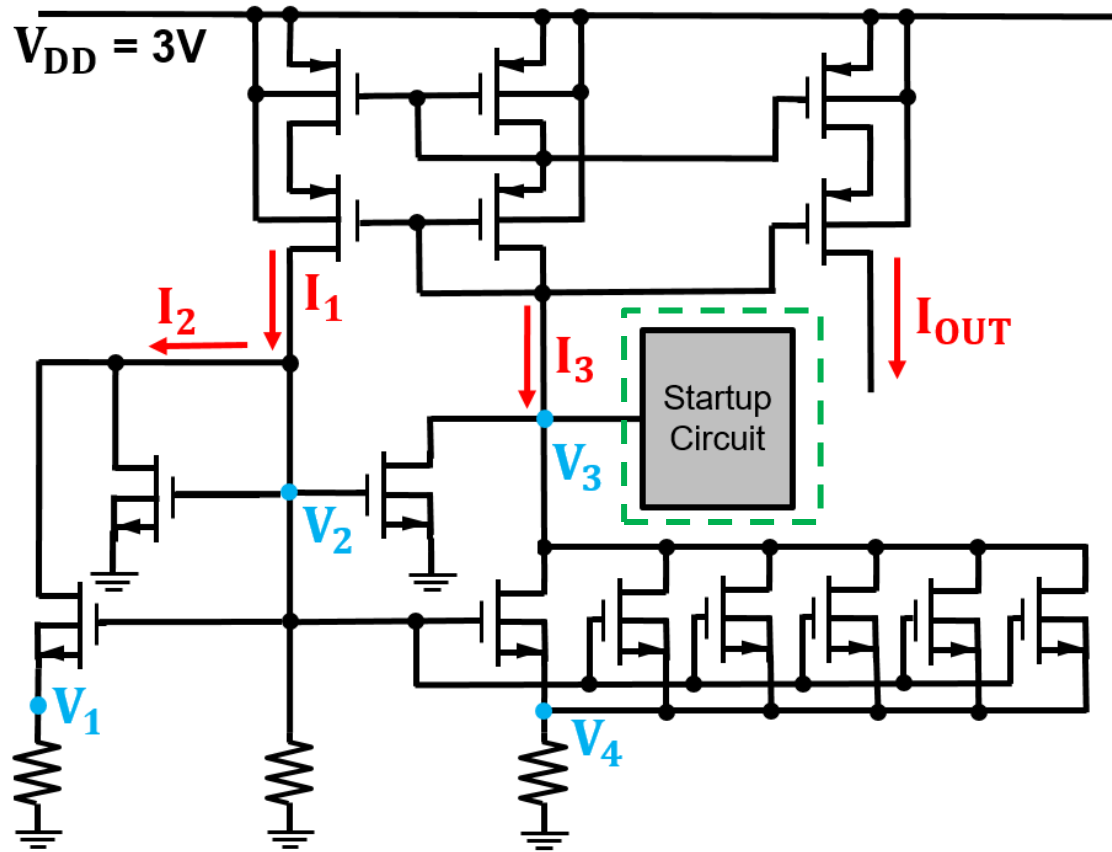


# OUTLINE

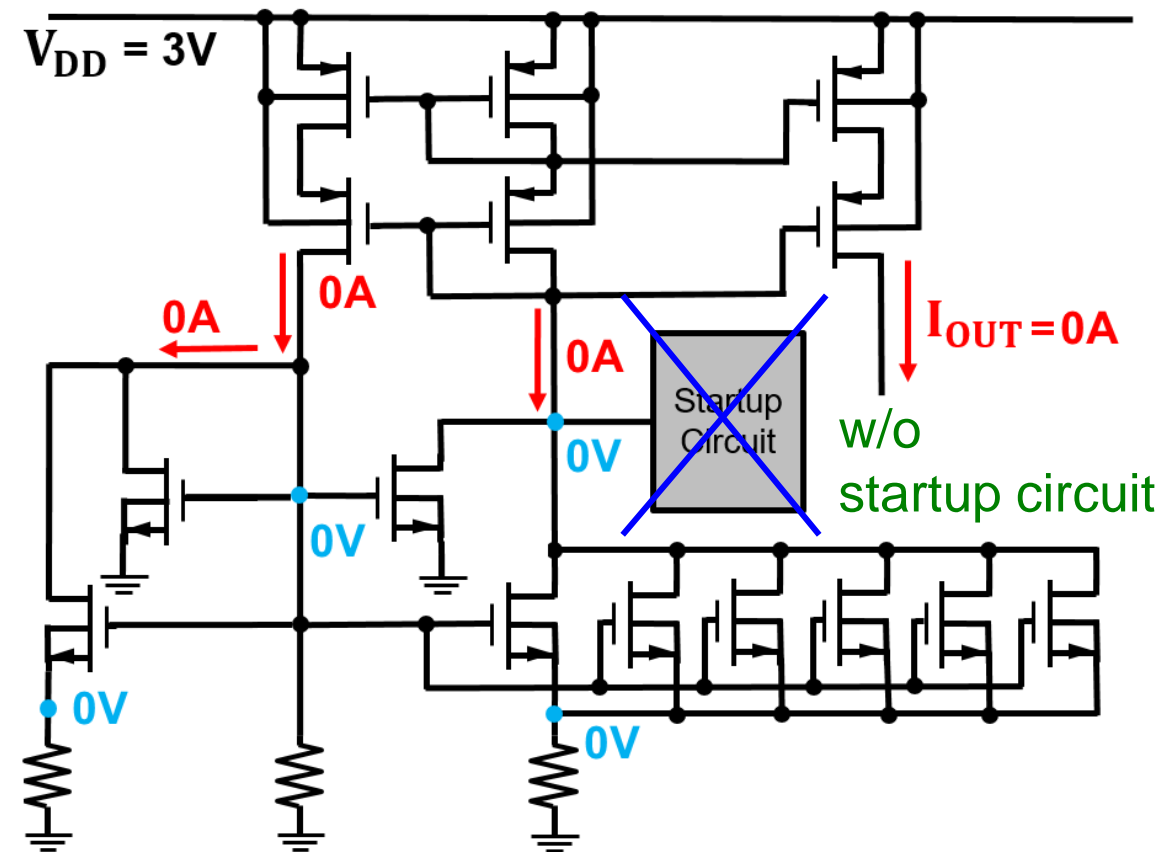
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# Need for Startup Circuits



$I_{OUT}$  conduction state  
Proper operation



$I_{OUT} = 0$   
Malfunction

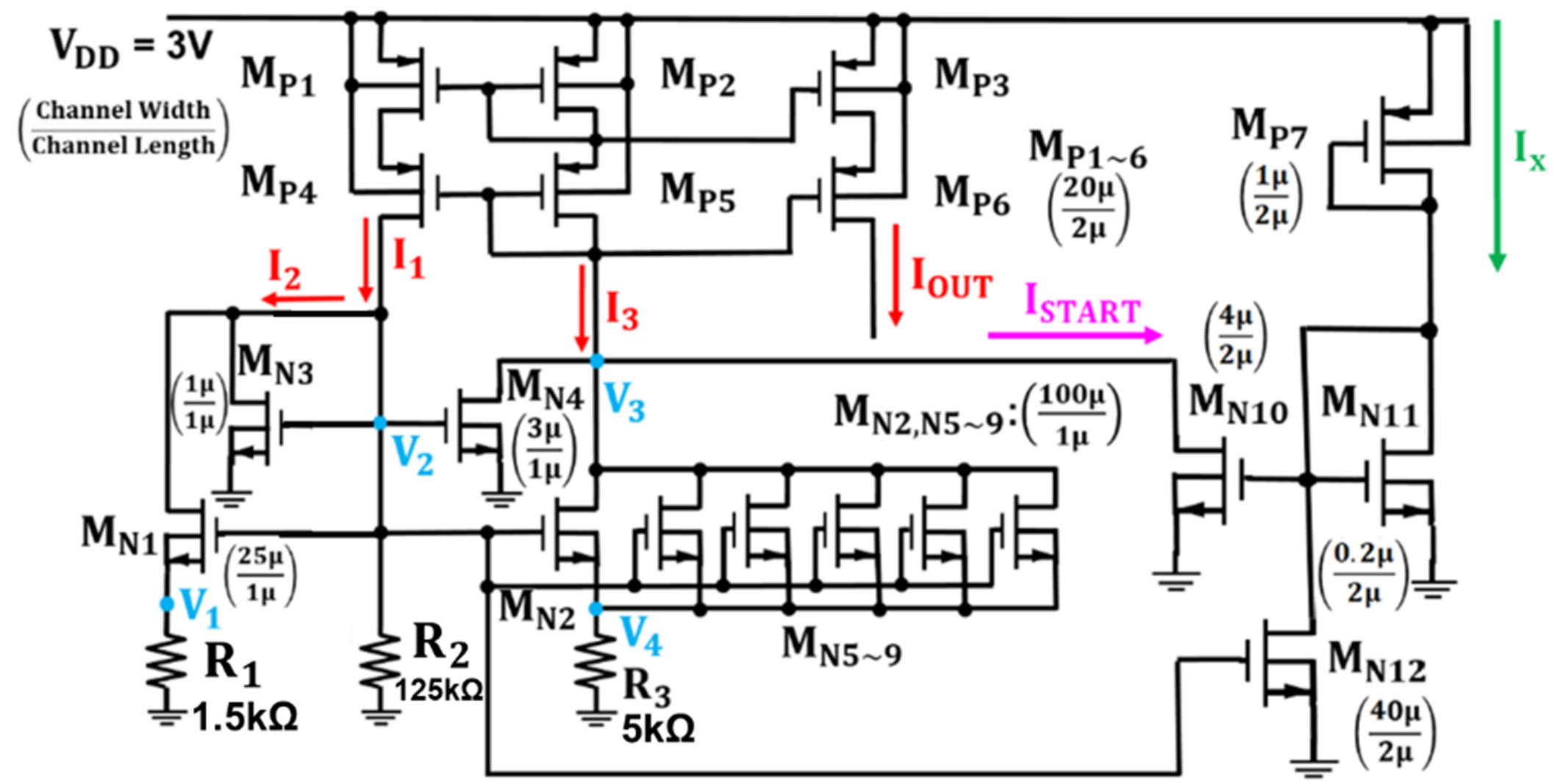
Compared Three Types of Startup Circuit in terms of **Chip area**, **Power consumption**, and **Startup operation certainty**.

# OUTLINE

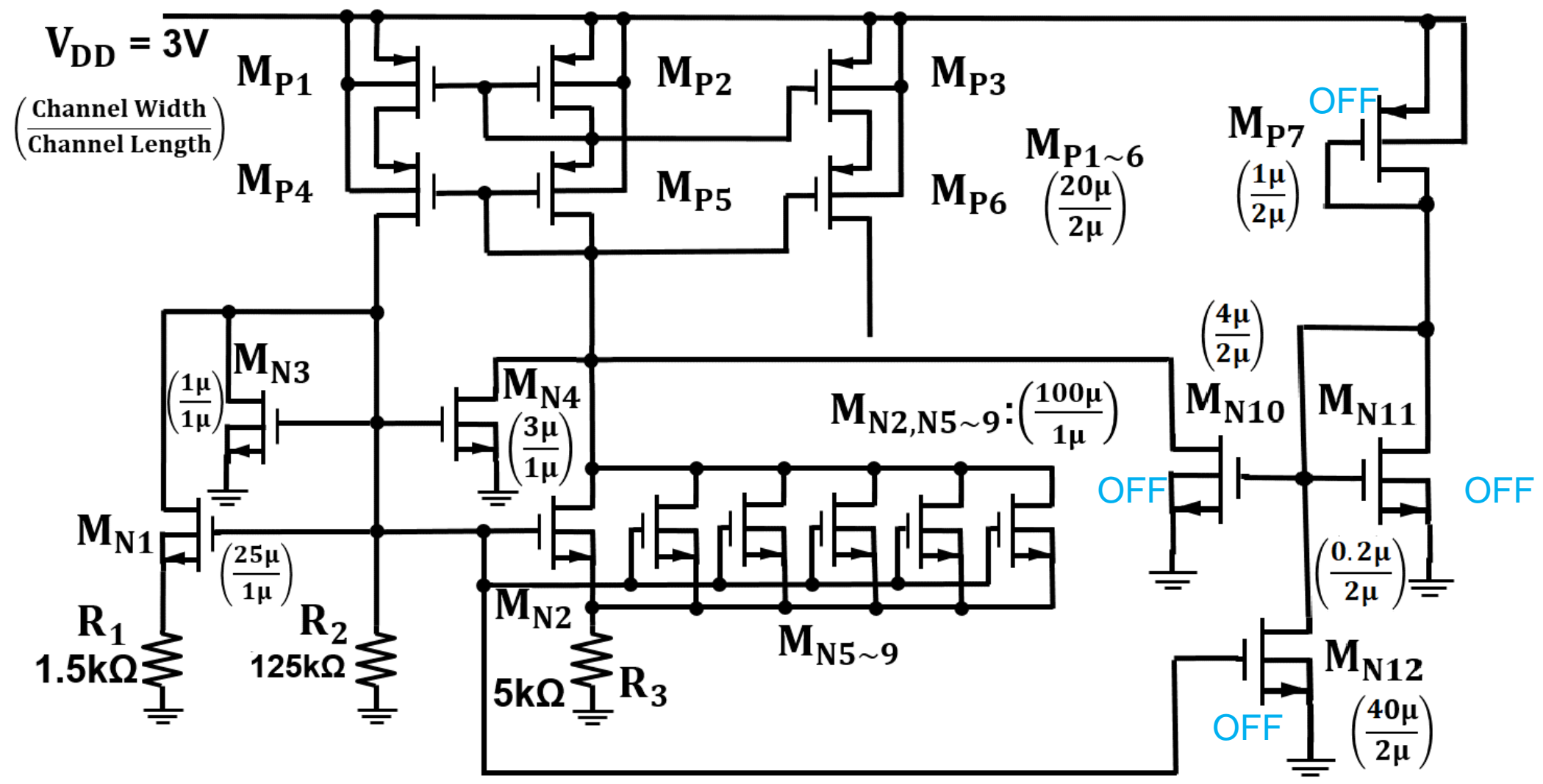
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# Startup Circuit 1

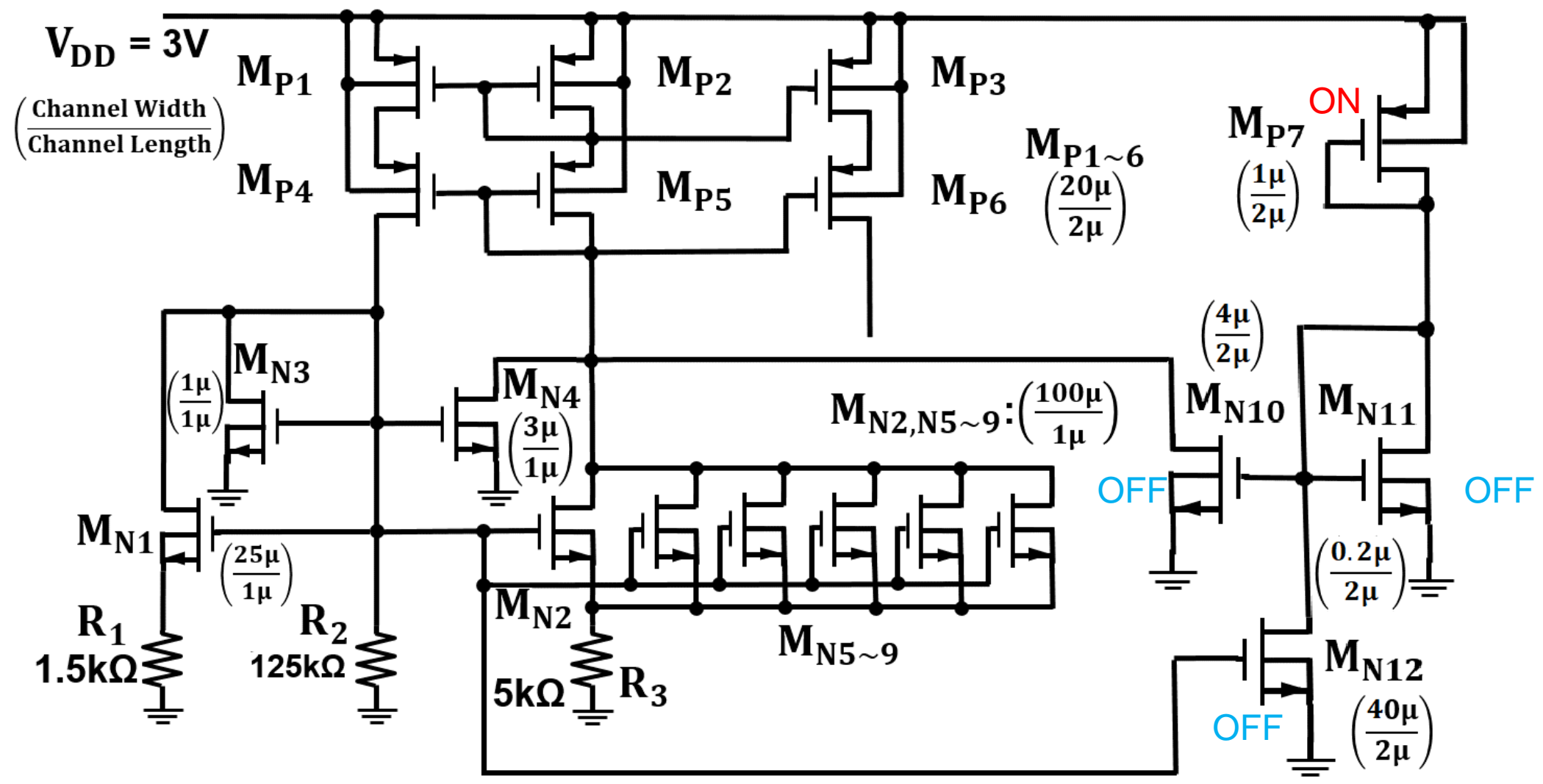


# Operation of Startup Circuit 1 (All node 0V)

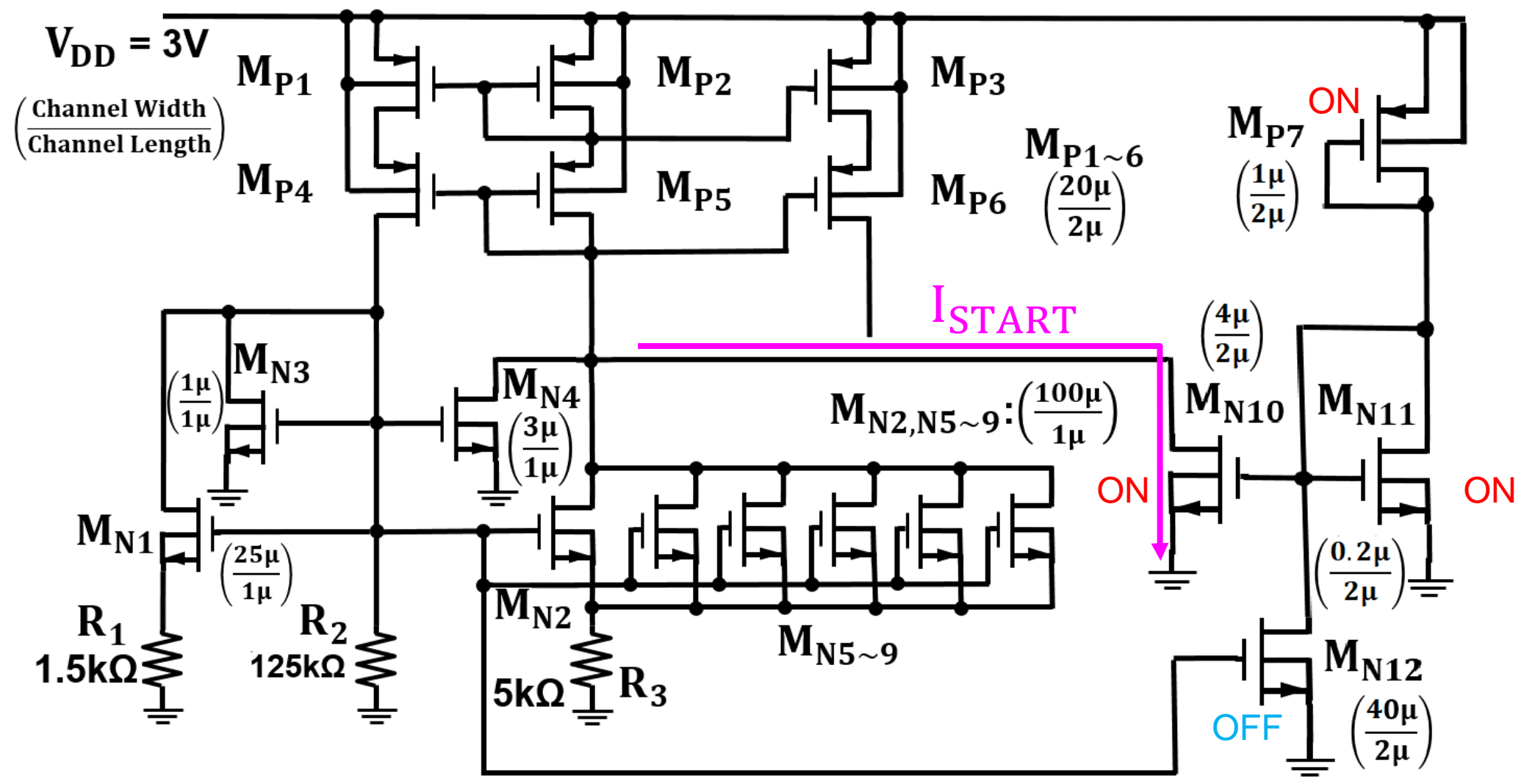




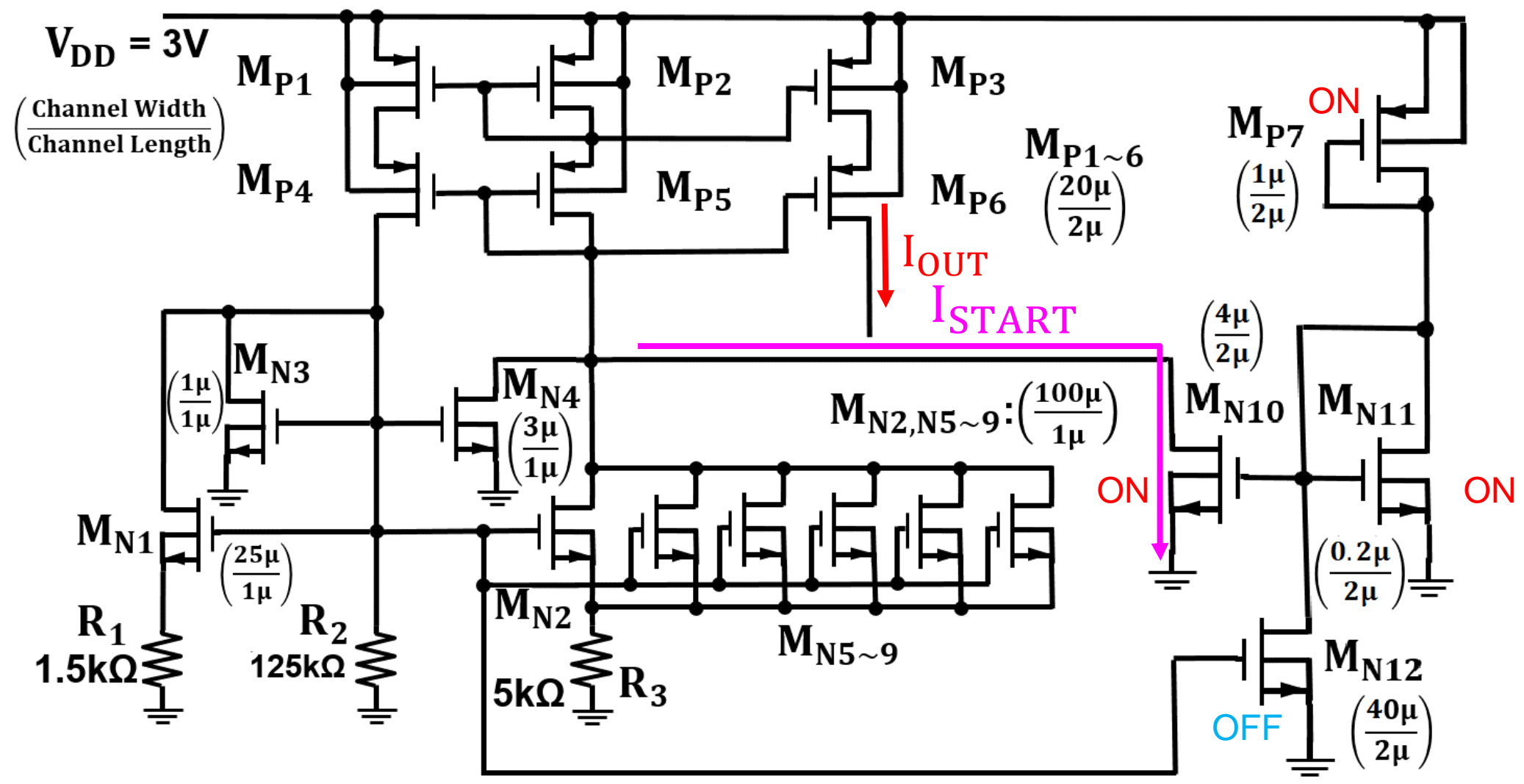
# Operation of Startup Circuit 1 ( $M_{P7}$ ON)



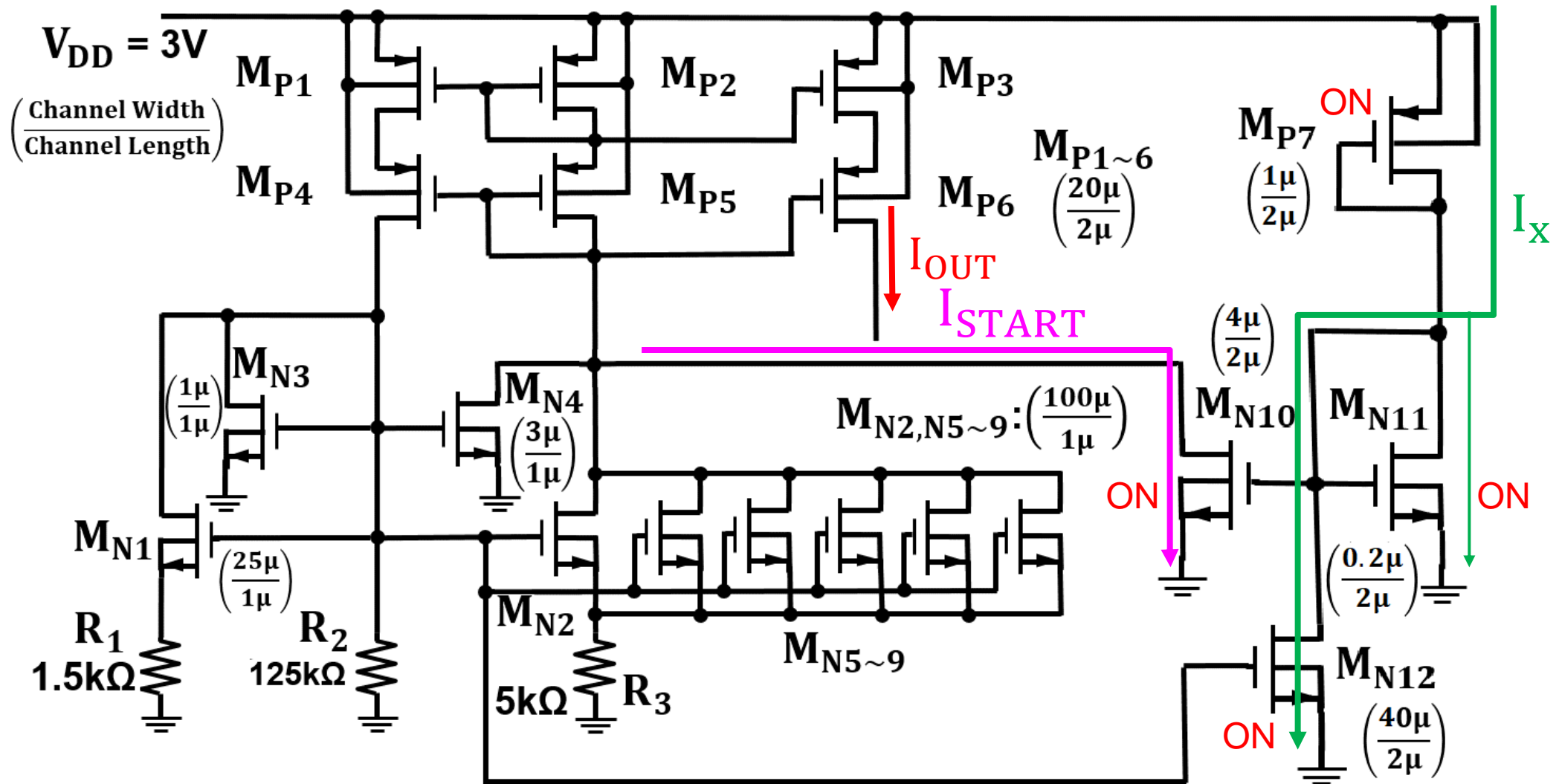
# Operation of Startup Circuit 1 ( $M_{N10}$ ON)



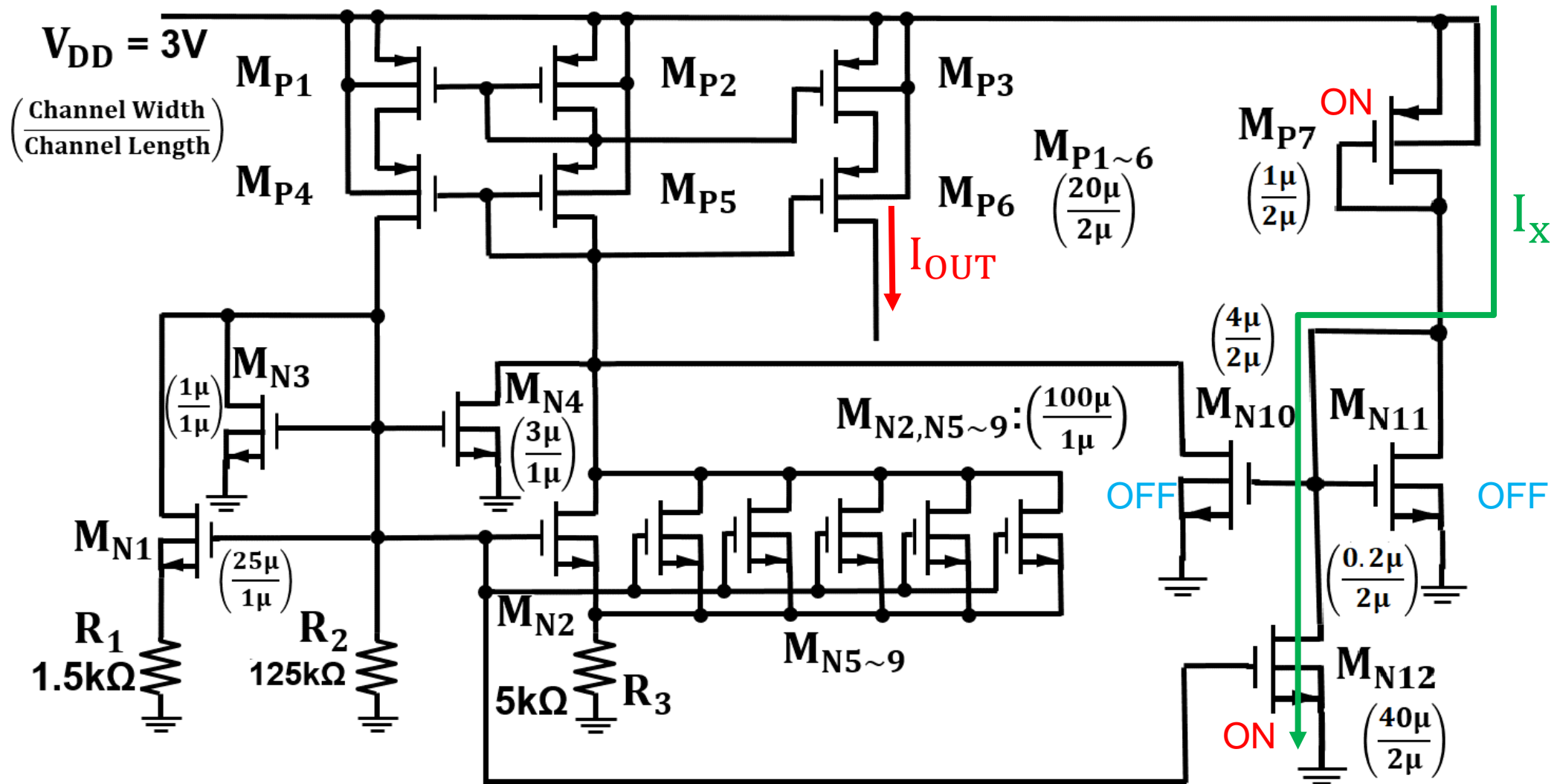
# Operation of Startup Circuit 1 ( $I_{OUT}$ flow)



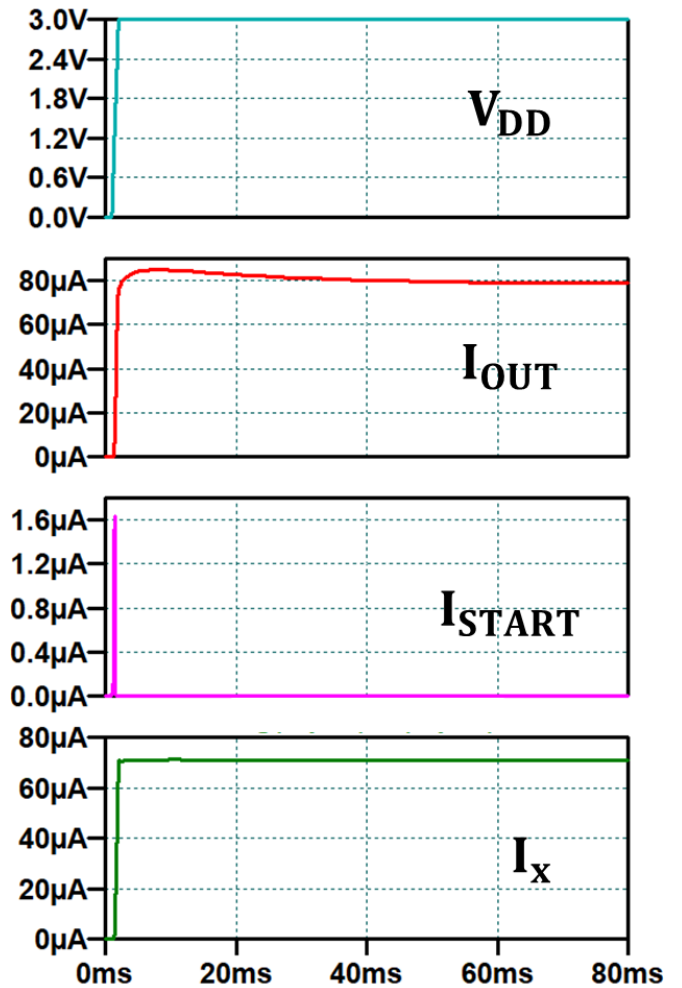
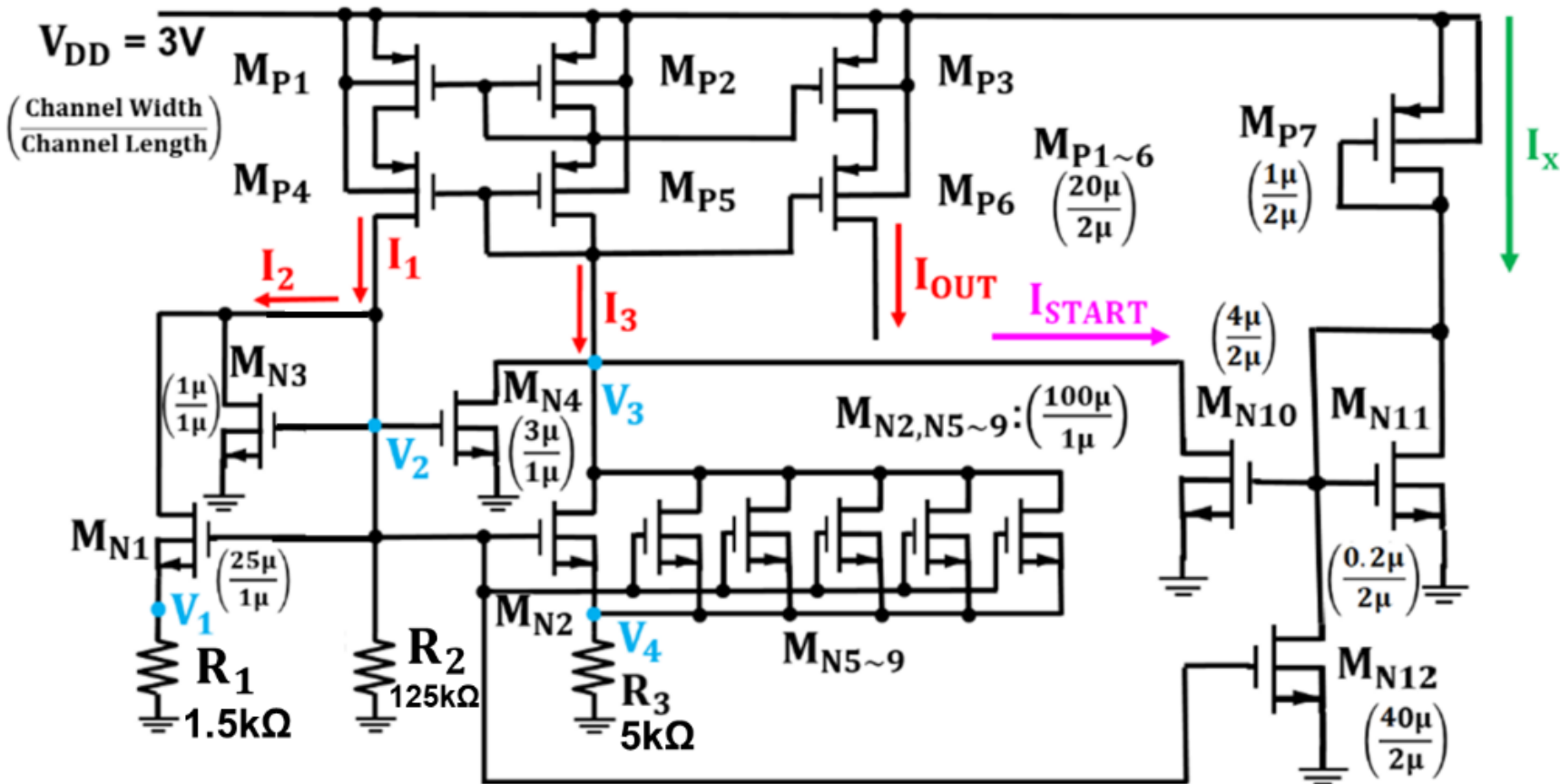
# Operation of Startup Circuit 1 ( $M_{N12}$ ON)



# Operation of Startup Circuit 1 ( $M_{N10}$ OFF)



# Demerit of Startup Circuit 1



Demerit (⊖)

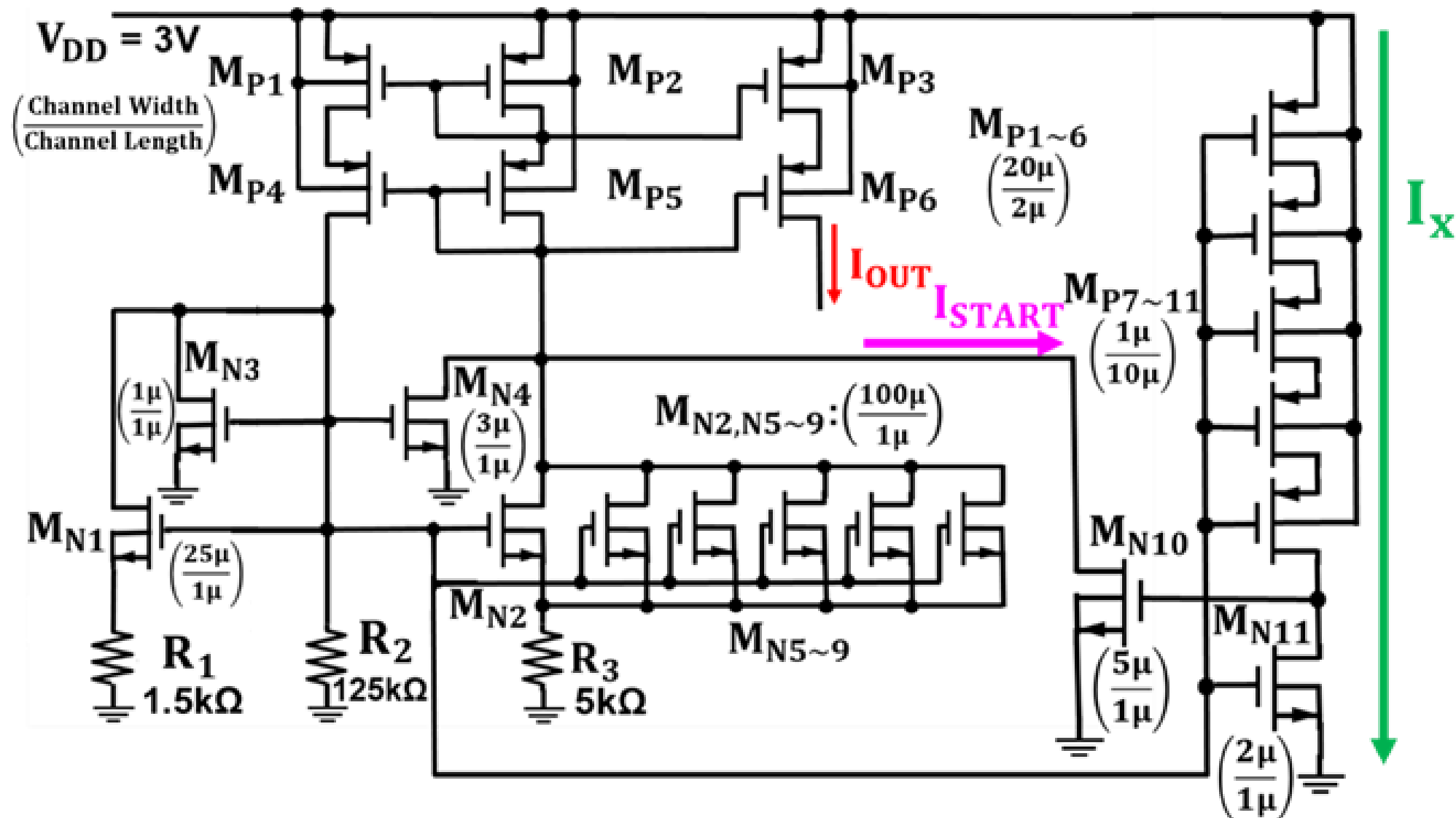
- Large power consumption

# OUTLINE

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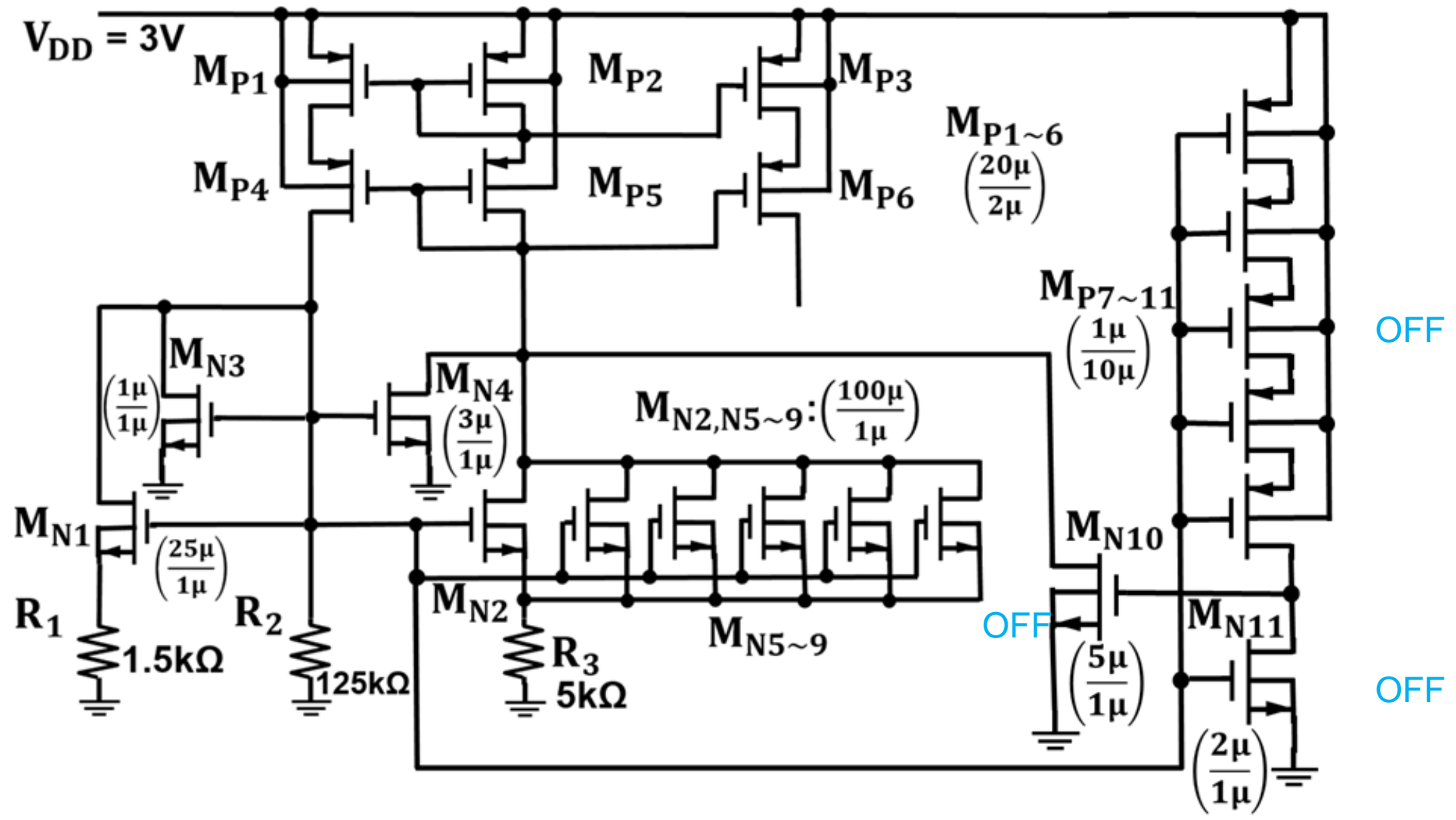
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# Startup Circuit 2 (CMOS inverter usage)

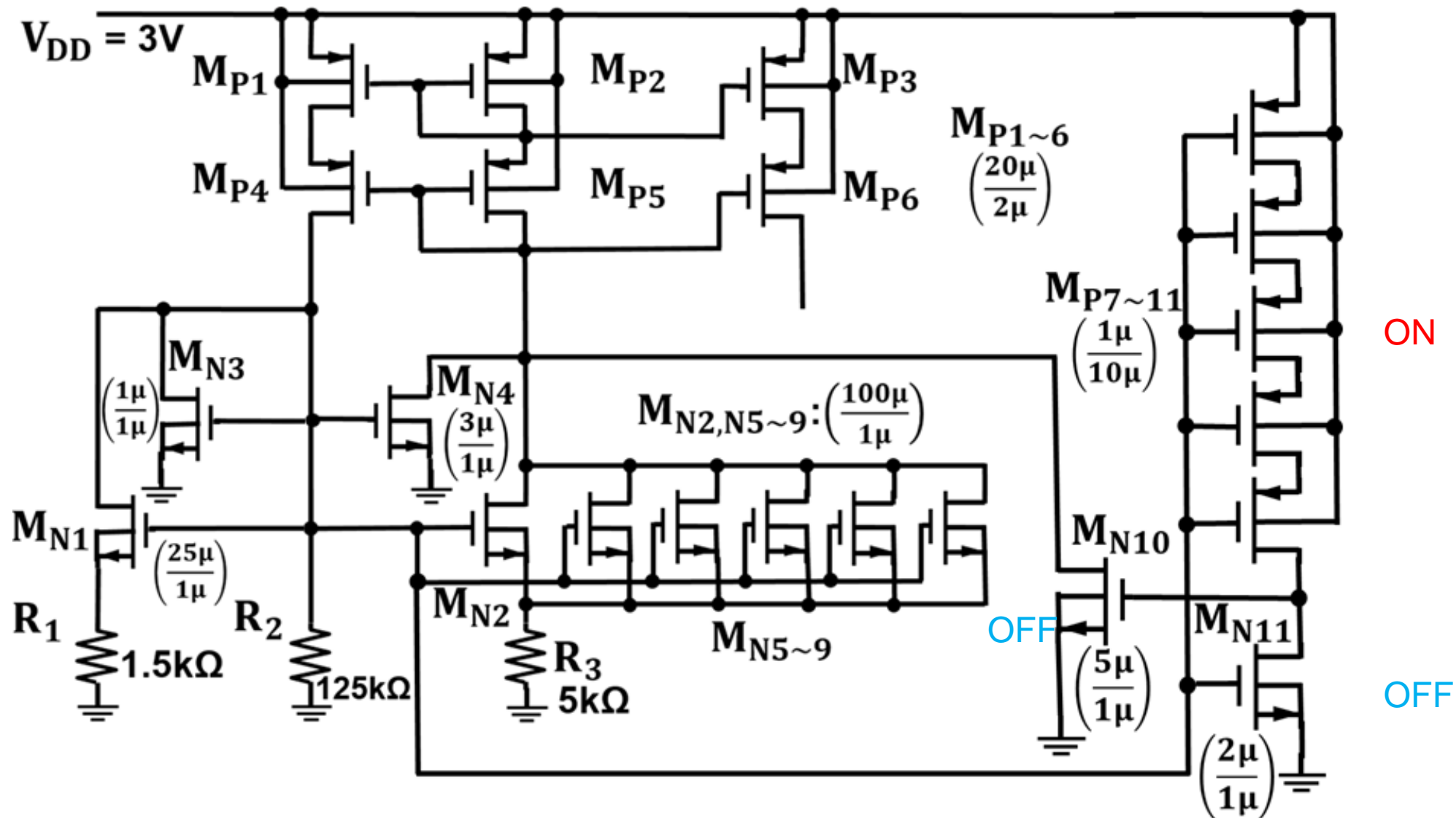




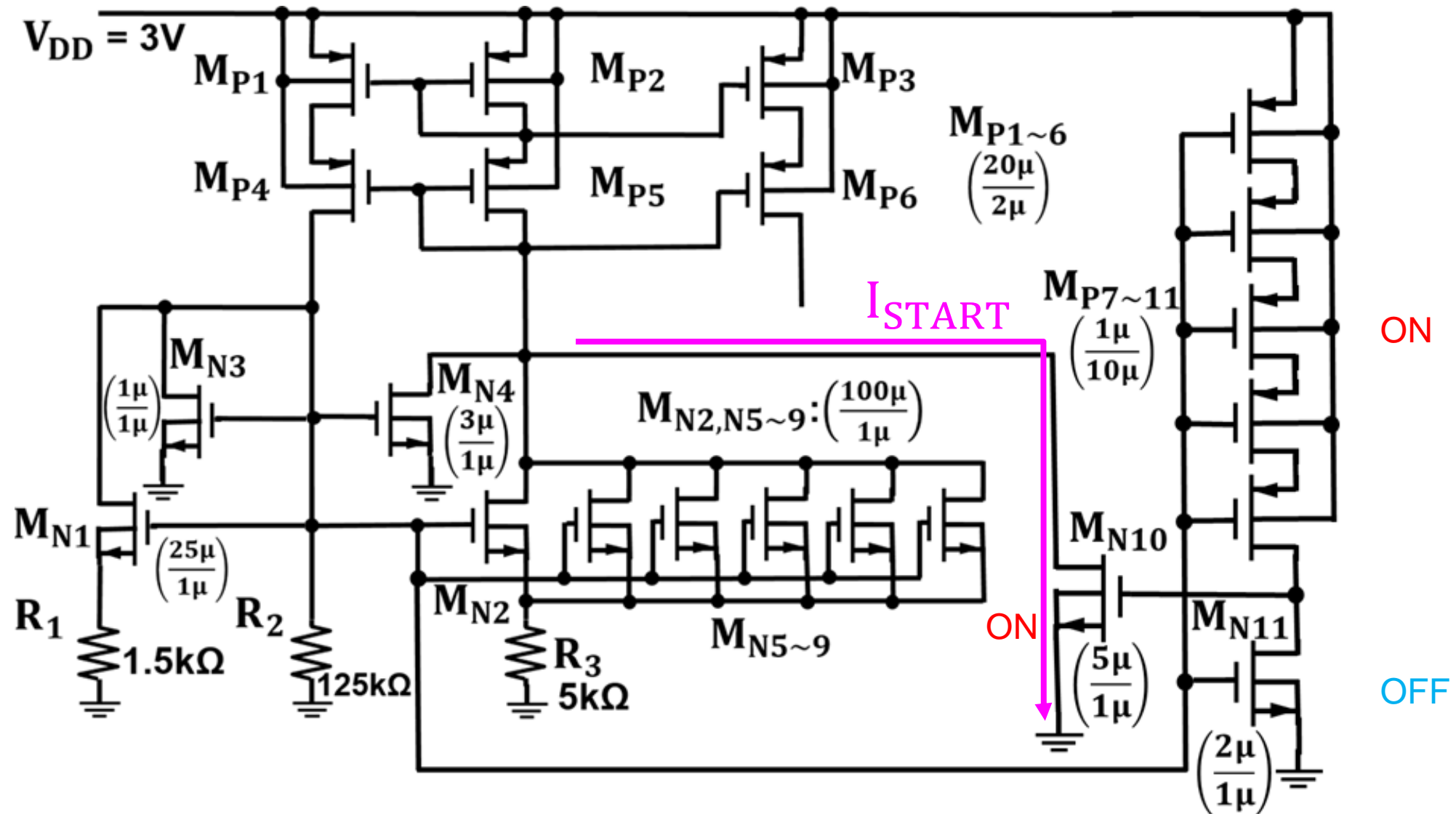
# Operation of Startup Circuit 2 (All node 0V)



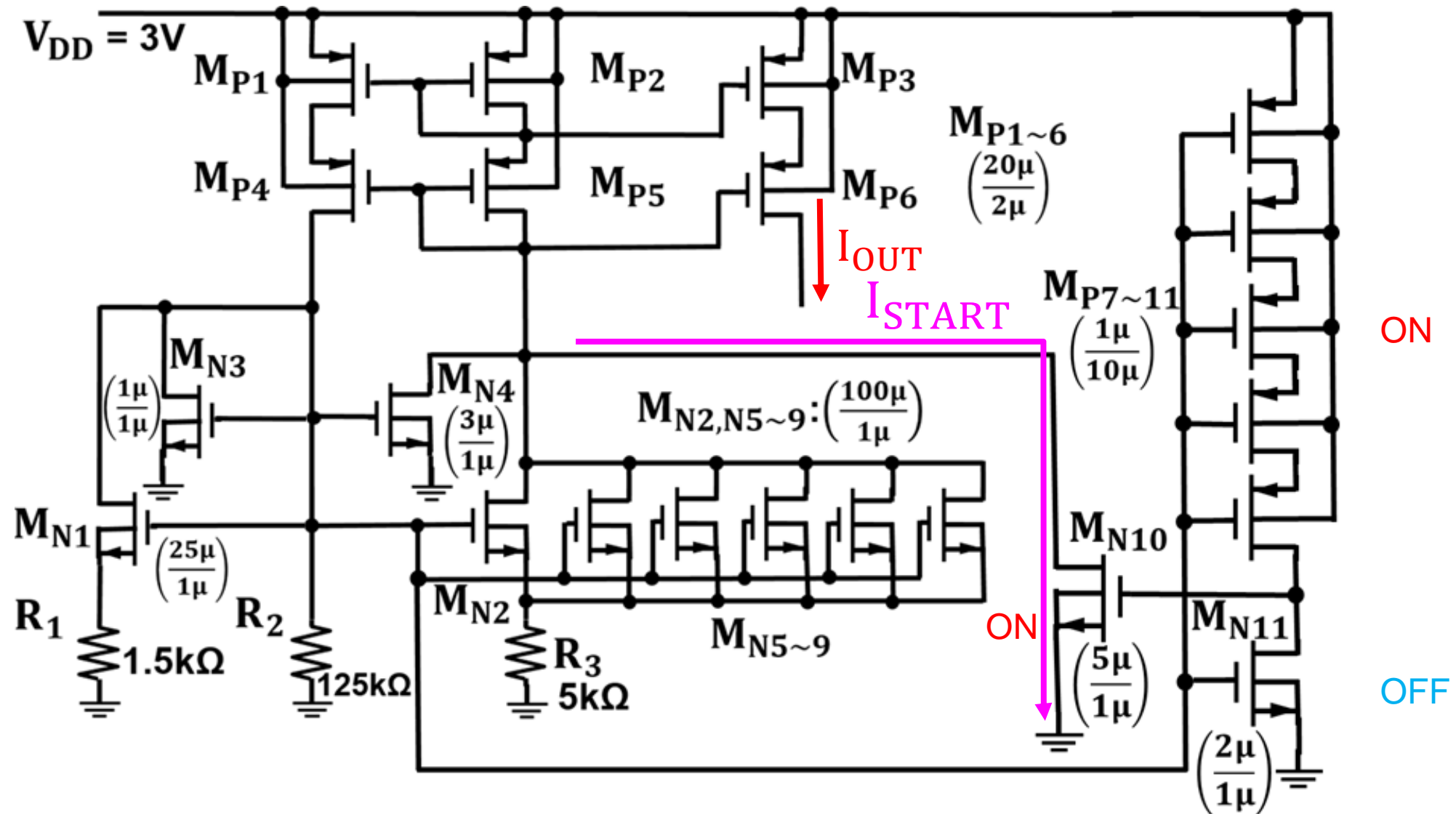
# Operation of Startup Circuit 2 ( $M_{P7\sim 11}$ ON)



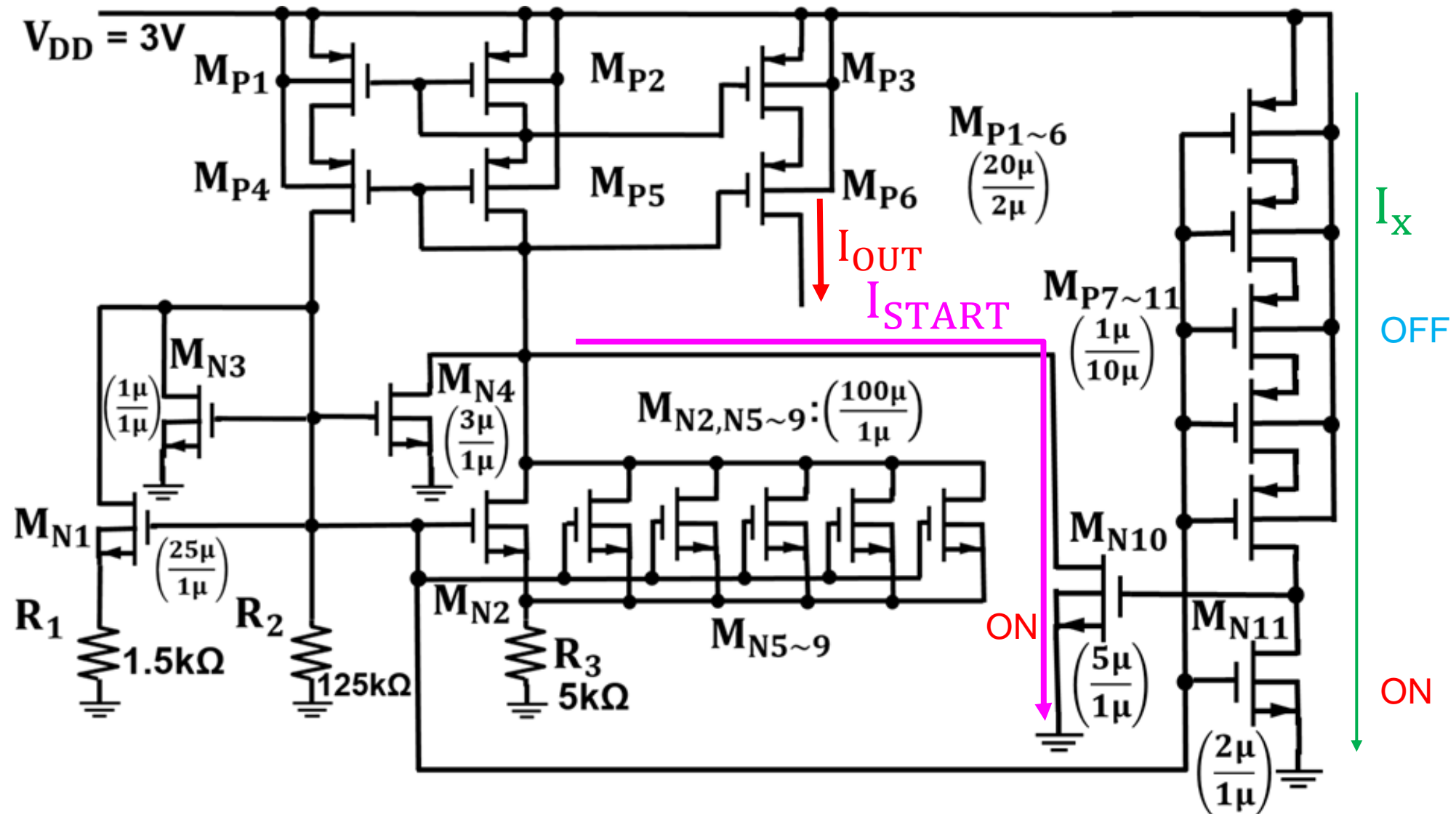
# Operation of Startup Circuit 2 ( $M_{N10}$ ON)



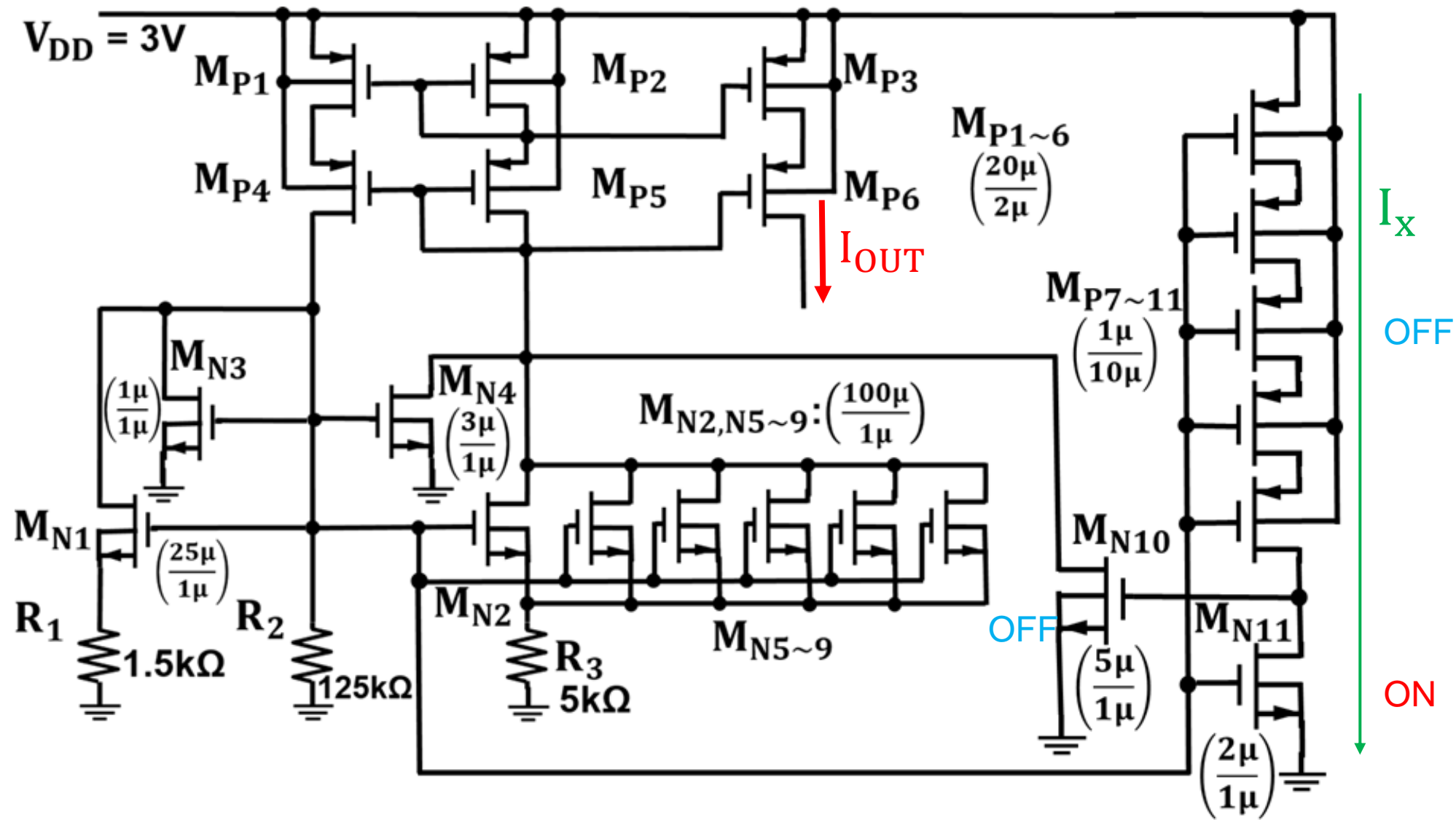
# Operation of Startup Circuit 2 ( $I_{OUT}$ flow)



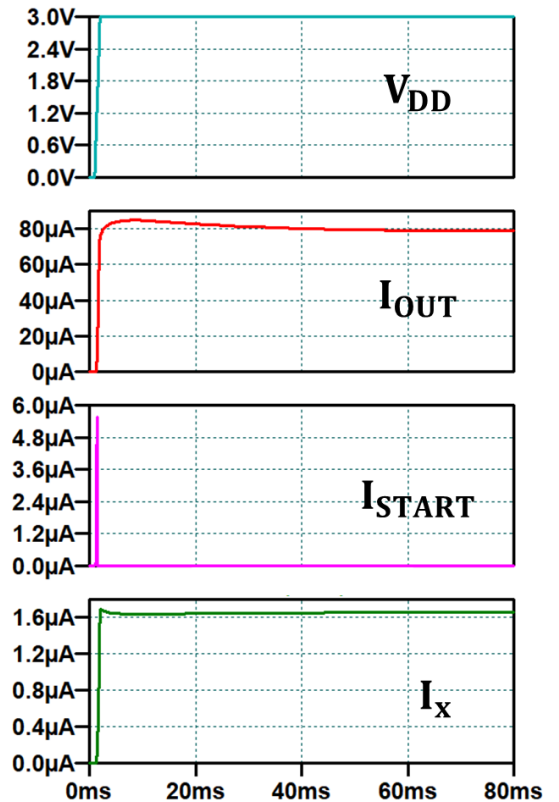
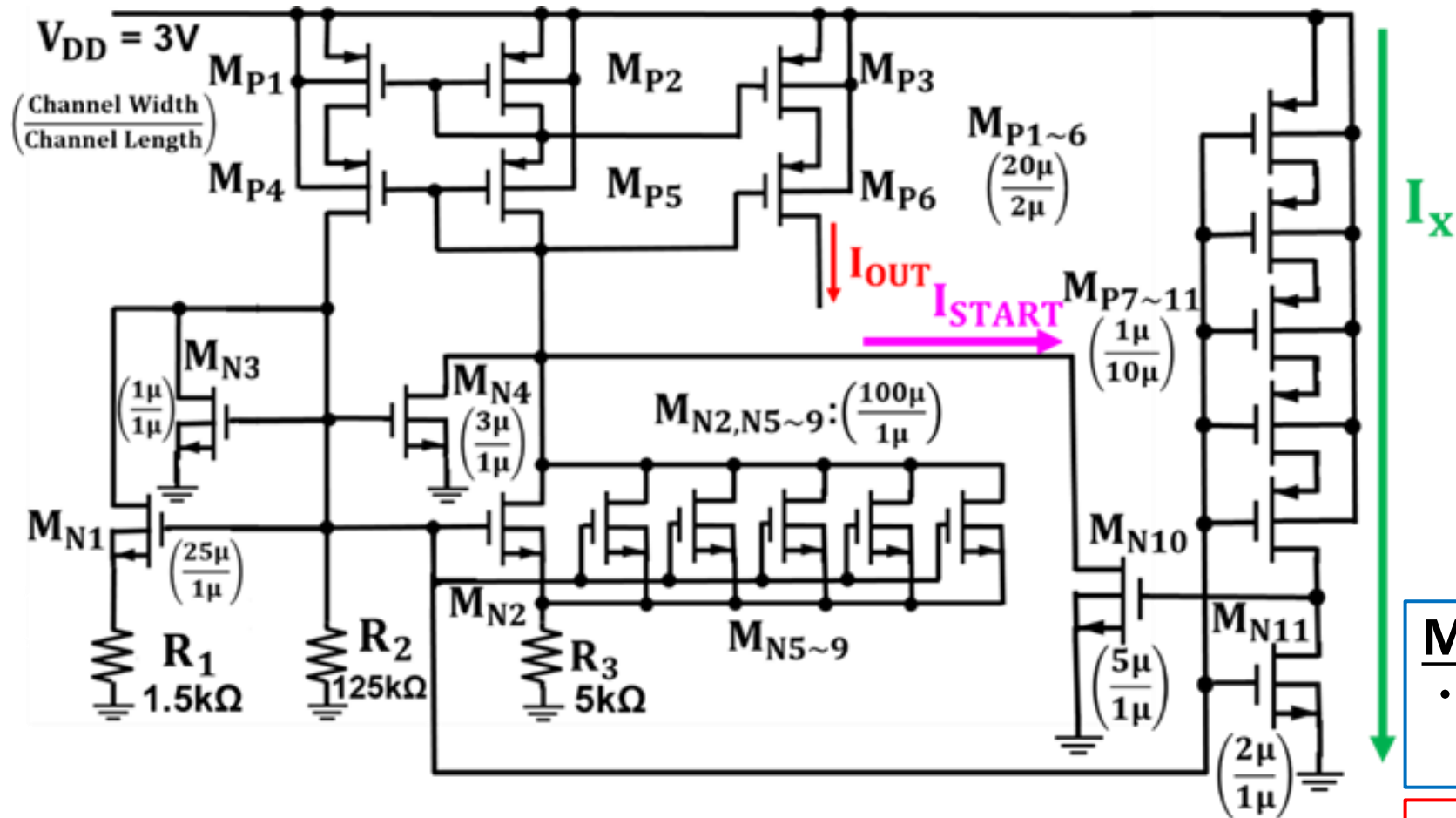
# Operation of Startup Circuit 2 ( $M_{P7\sim 11}$ OFF, $M_{N11}$ ON)



# Operation of Startup Circuit 2 ( $M_{N10}$ OFF)



# Merit and Demerit of Startup Circuit 2



**Merit** ☺

- Some reduction in power consumption

**Demerit** ☹

- Some increase in chip area

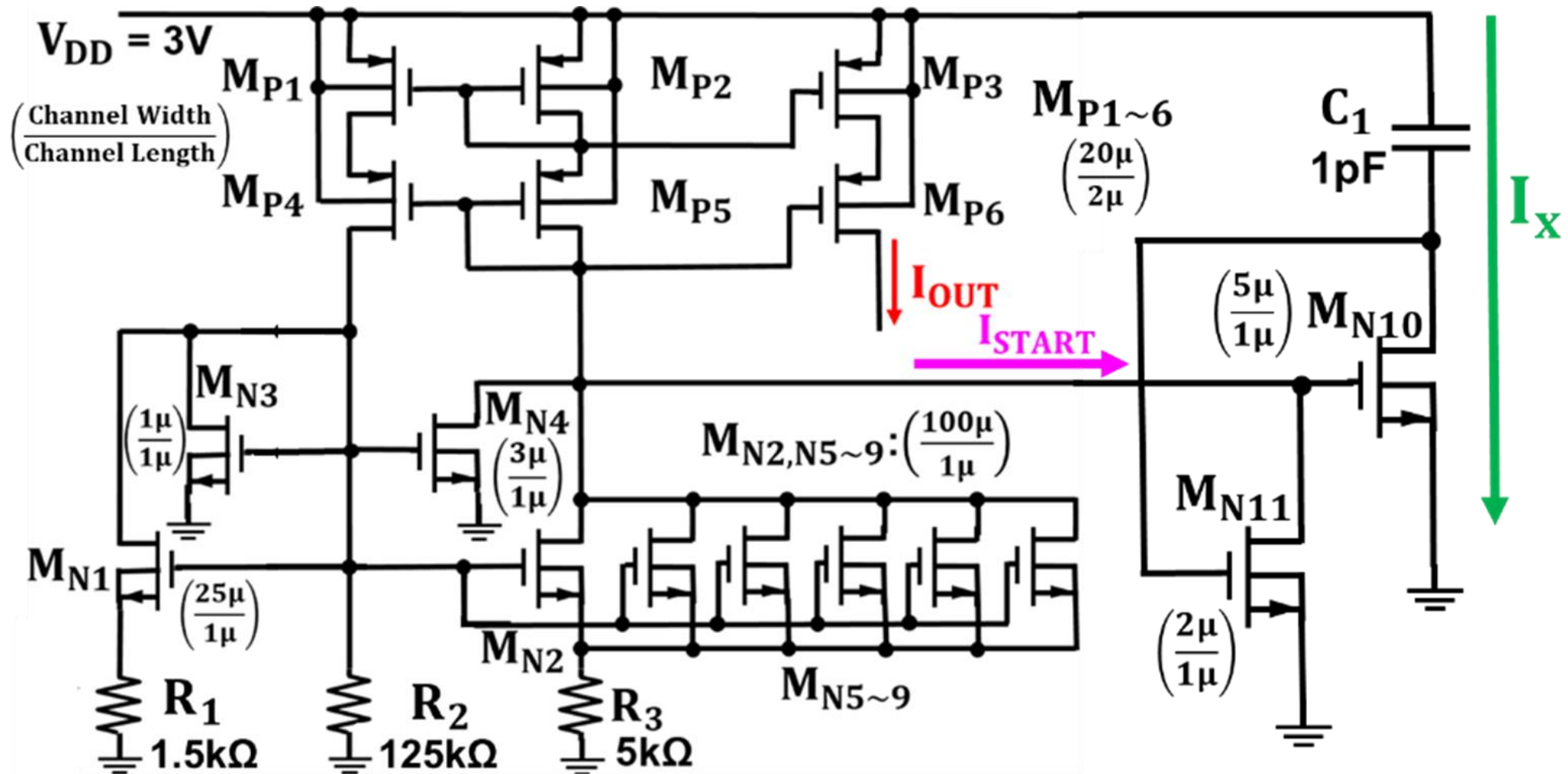
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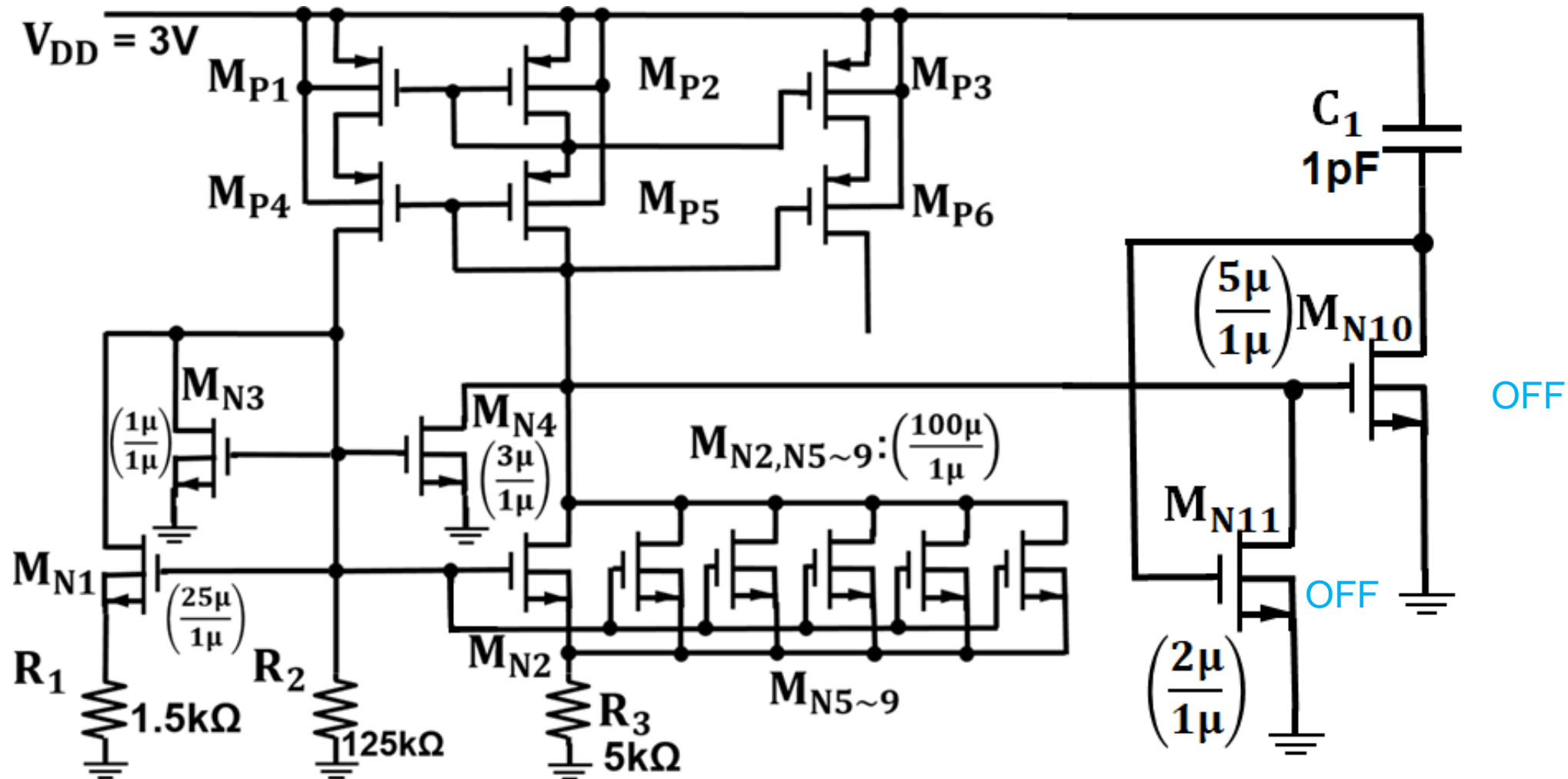
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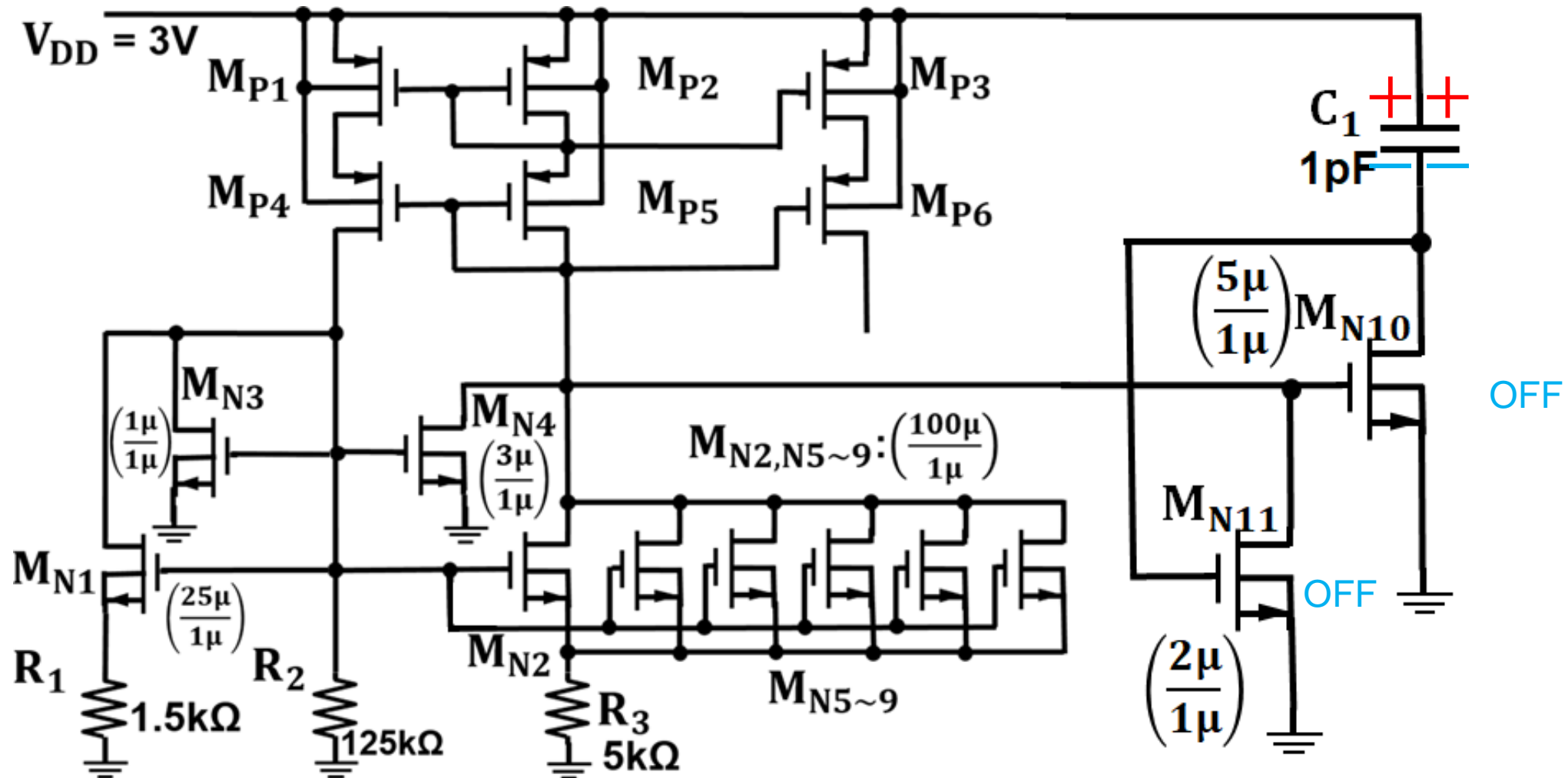
# Startup Circuit 3 (Capacitor usage)



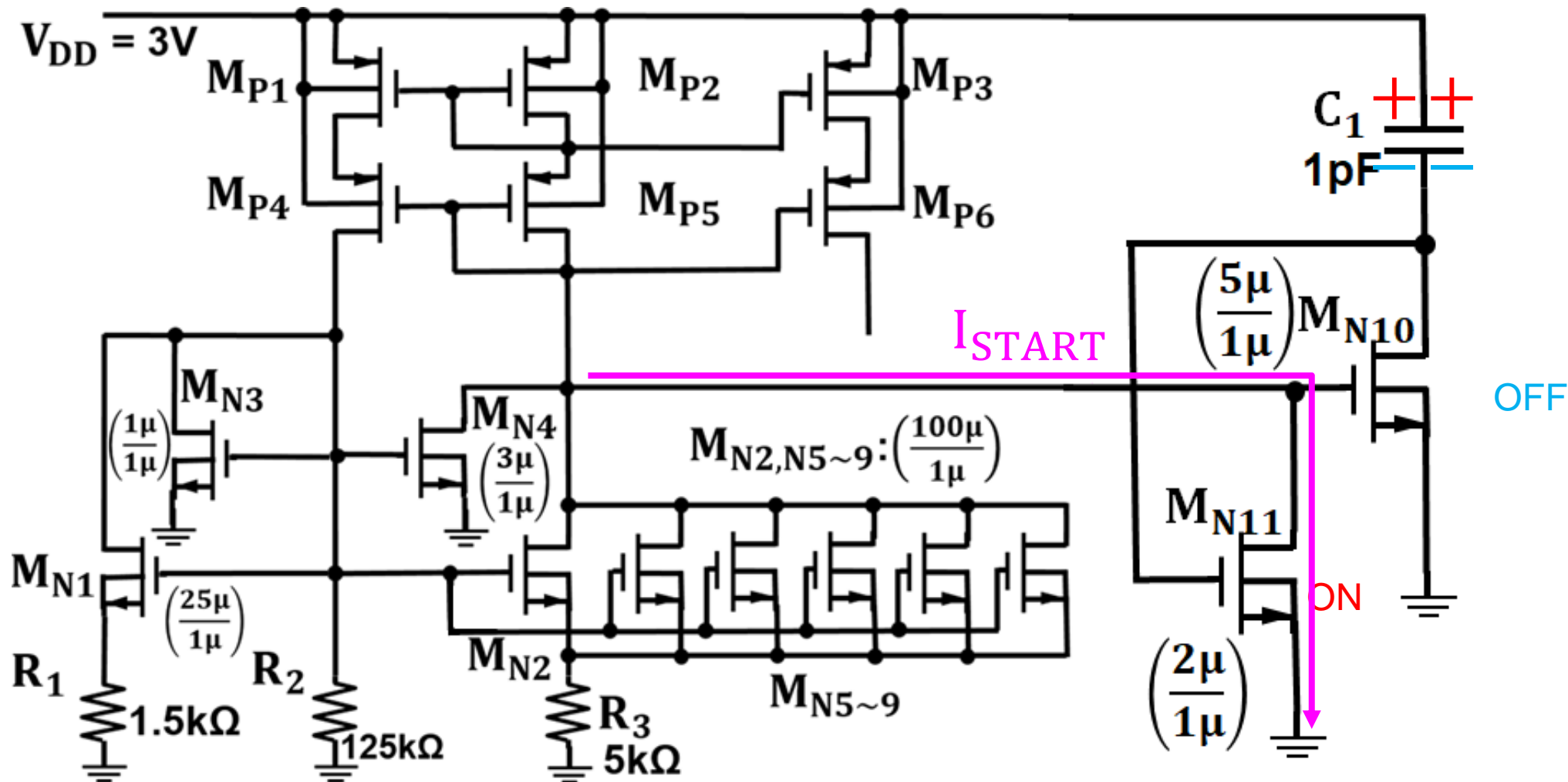
# Operation of Startup Circuit 3 (All node 0V)



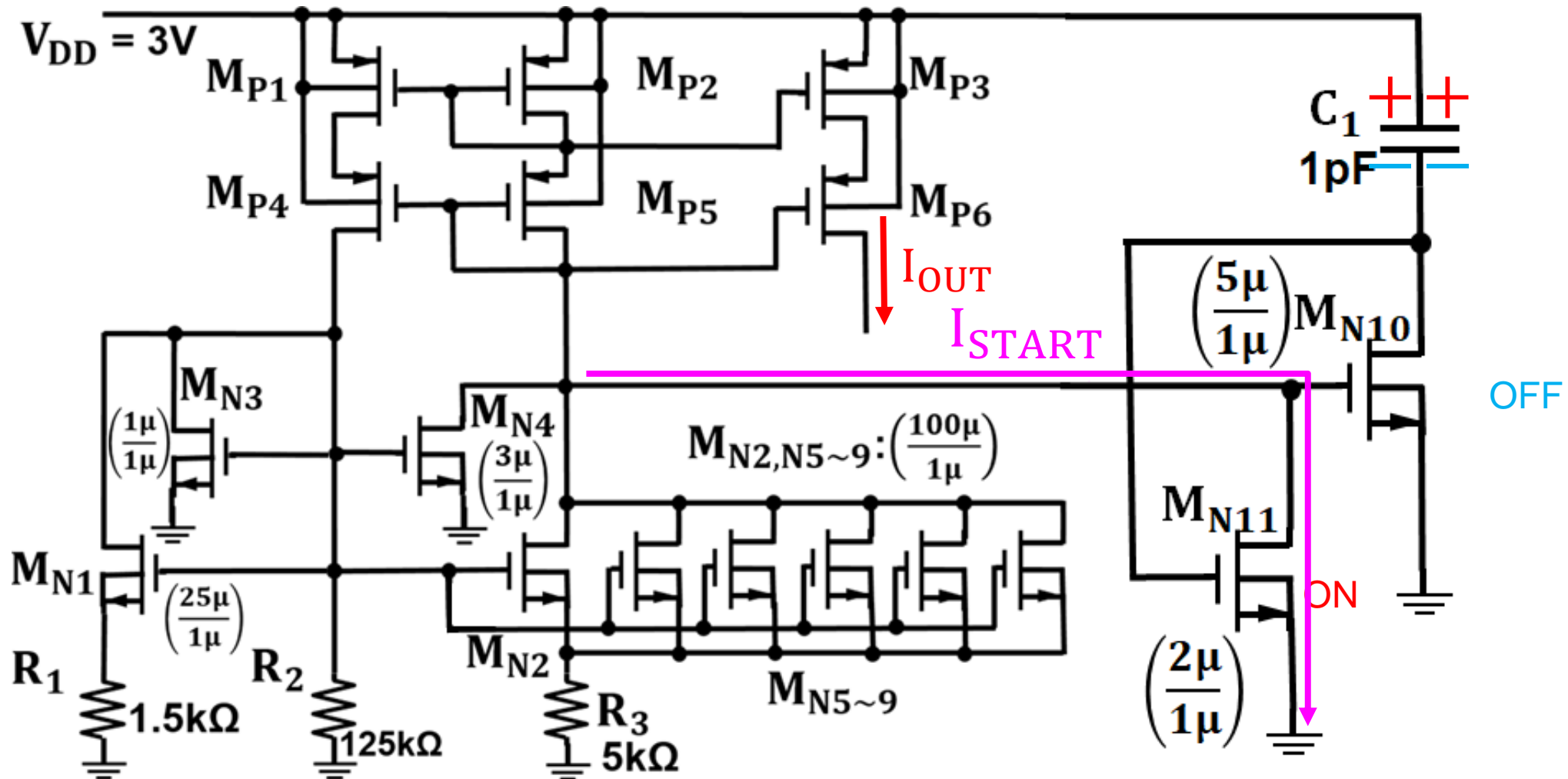
# Operation of Startup Circuit 3 ( $C_1$ Charged)



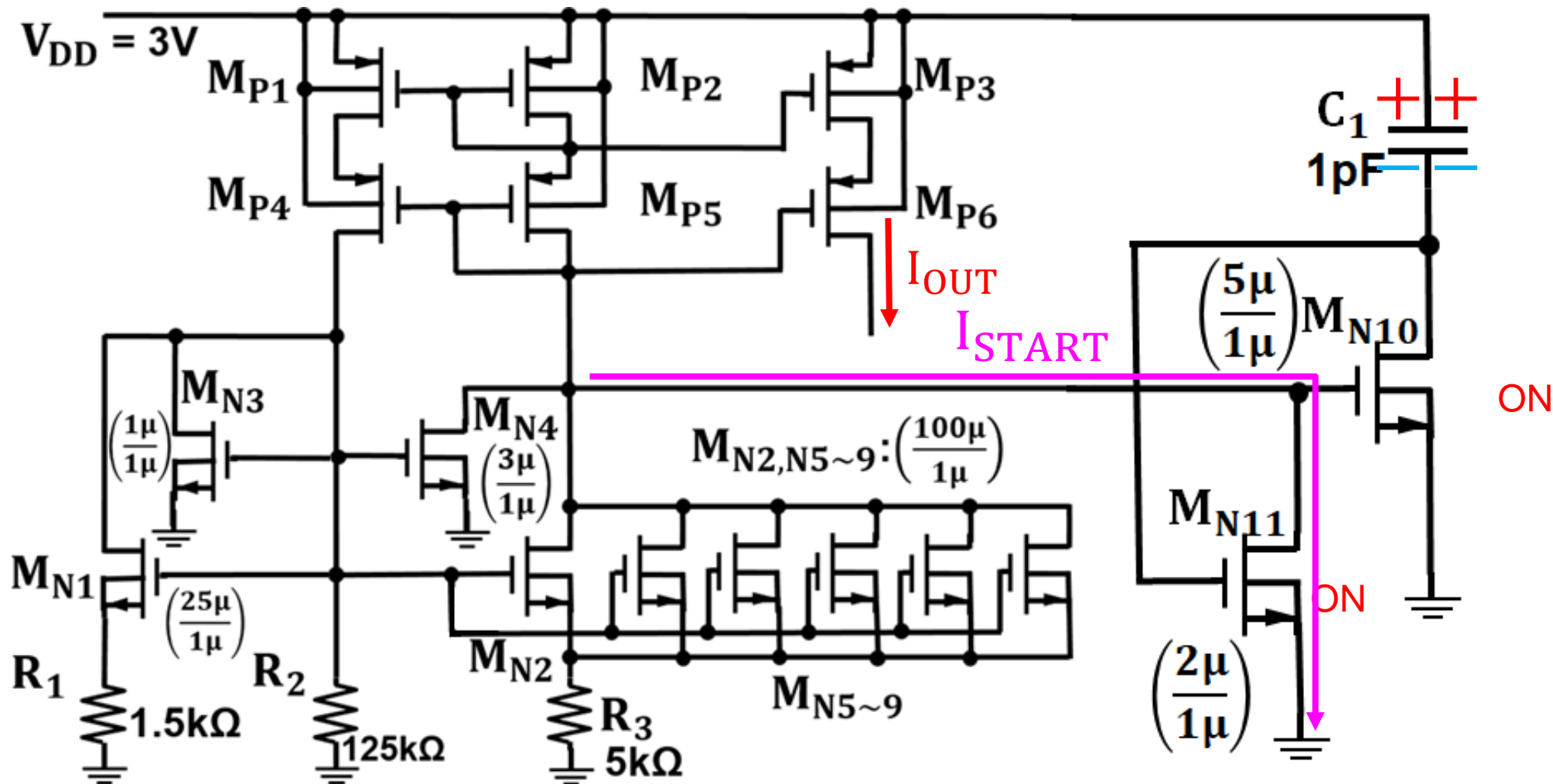
# Operation of Startup Circuit 3 ( $M_{N11}$ ON)



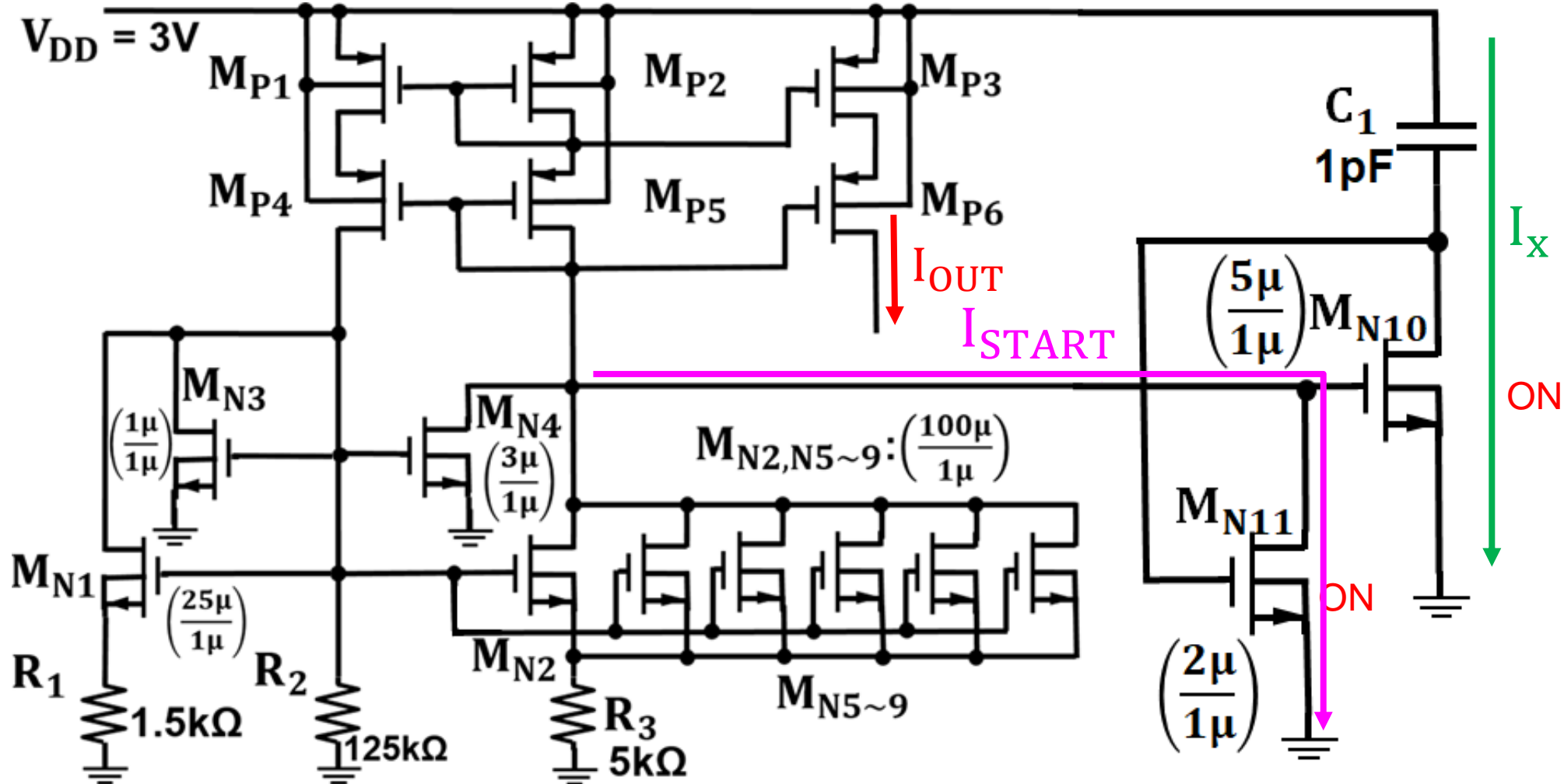
# Operation of Startup Circuit 3 ( $I_{O_{UT}}$ flow)



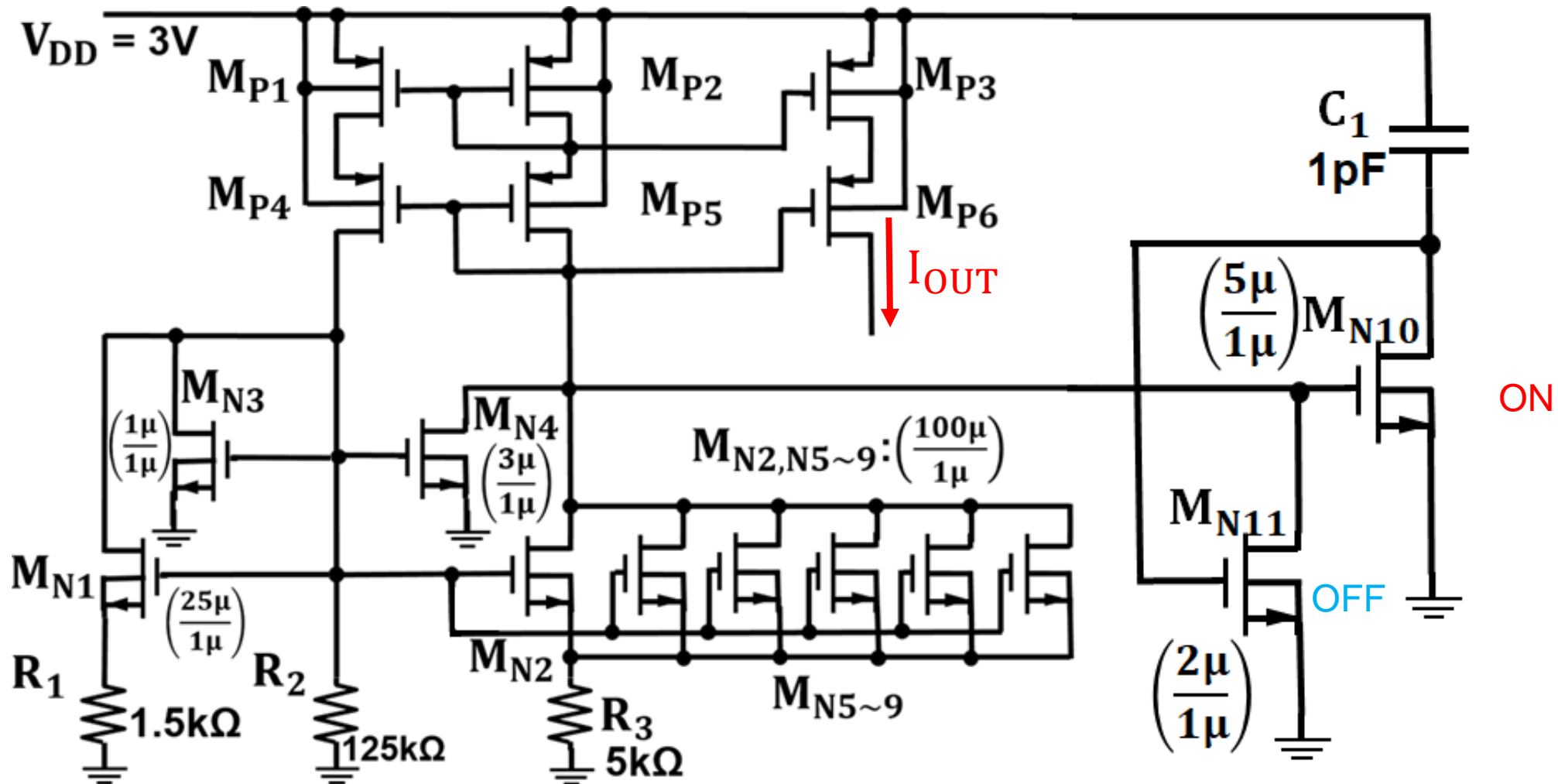
# Operation of Startup Circuit 3 ( $M_{N10}$ ON)



# Operation of Startup Circuit 3 ( $C_1$ discharged)

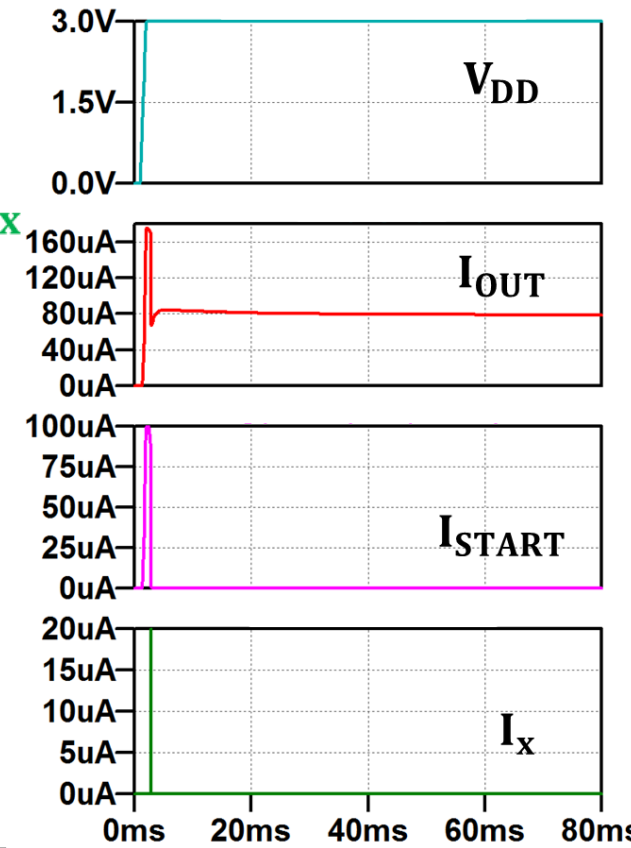
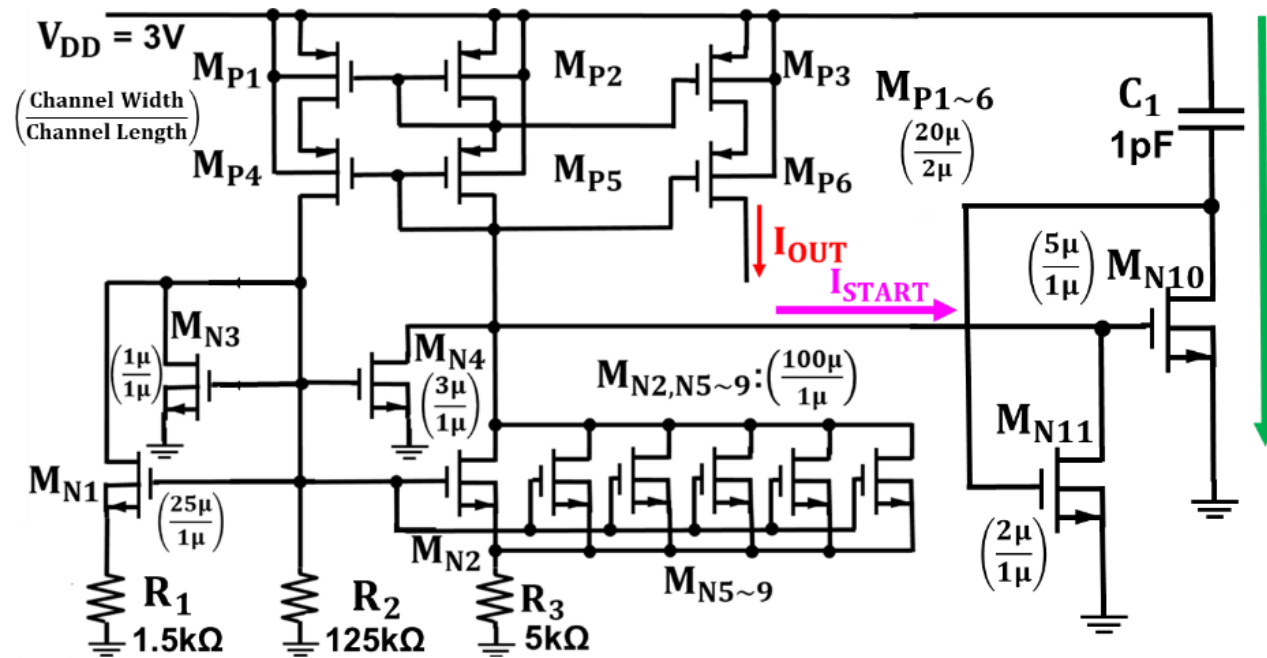


# Operation of Startup Circuit 3 ( $M_{N11}$ OFF)

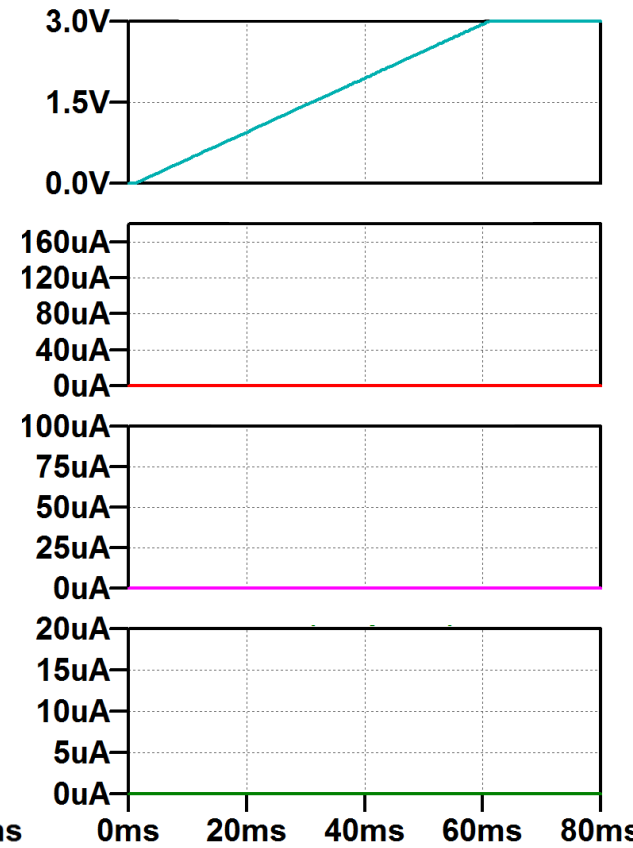




# Merit and Demerits of Startup Circuit 3



$V_{DD}$  rise time = 1ms



$V_{DD}$  rise time = 60ms

Capacitor model : GCH1555C1H1R0CE01  
of Murata Manufacturing Co., Ltd.

## Merit ☺

- Reduction in power consumption (If the rise of  $V_{DD}$  is fast)

## Demerits ☹

- Increase in chip area
- Problem of startup certainty

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# Conclusion and Challenges

## Conclusion

- The following table shows a comparison of startup circuits.

Types of startup circuits	Chip area	Power consumption	Startup certainty
Startup circuit 1	Good	Poor	Good
Startup circuit 2 (CMOS inverter usage)	Fair	Fair	Good
Startup circuit 3 (Capacitor usage)	Poor	Good	Poor

**Each startup circuit has its own advantages and disadvantages. It is necessary to select the optimal startup circuit according to the application of the proposed circuit.**

## Challenges

- Implementing a prototype chip.

# Acknowledgements

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Kobayashi  
Laboratory

**Thank you very much**